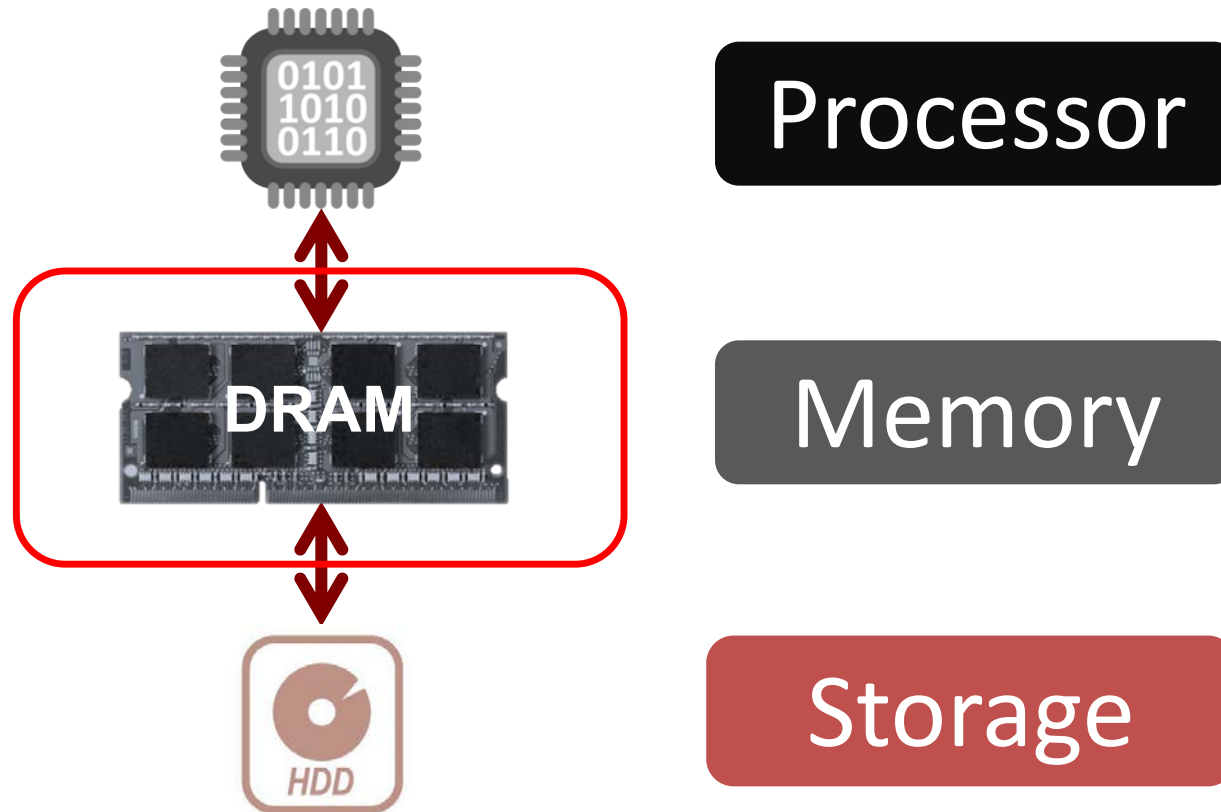


SOLVING THE DRAM SCALING CHALLENGE

Samira Khan



MEMORY IN TODAY'S SYSTEM



DRAM is critical for performance

TREND: DATA-INTENSIVE APPLICATIONS



DNA/PROTEIN
SYNTHESIS



IMAGE
ANALYSIS



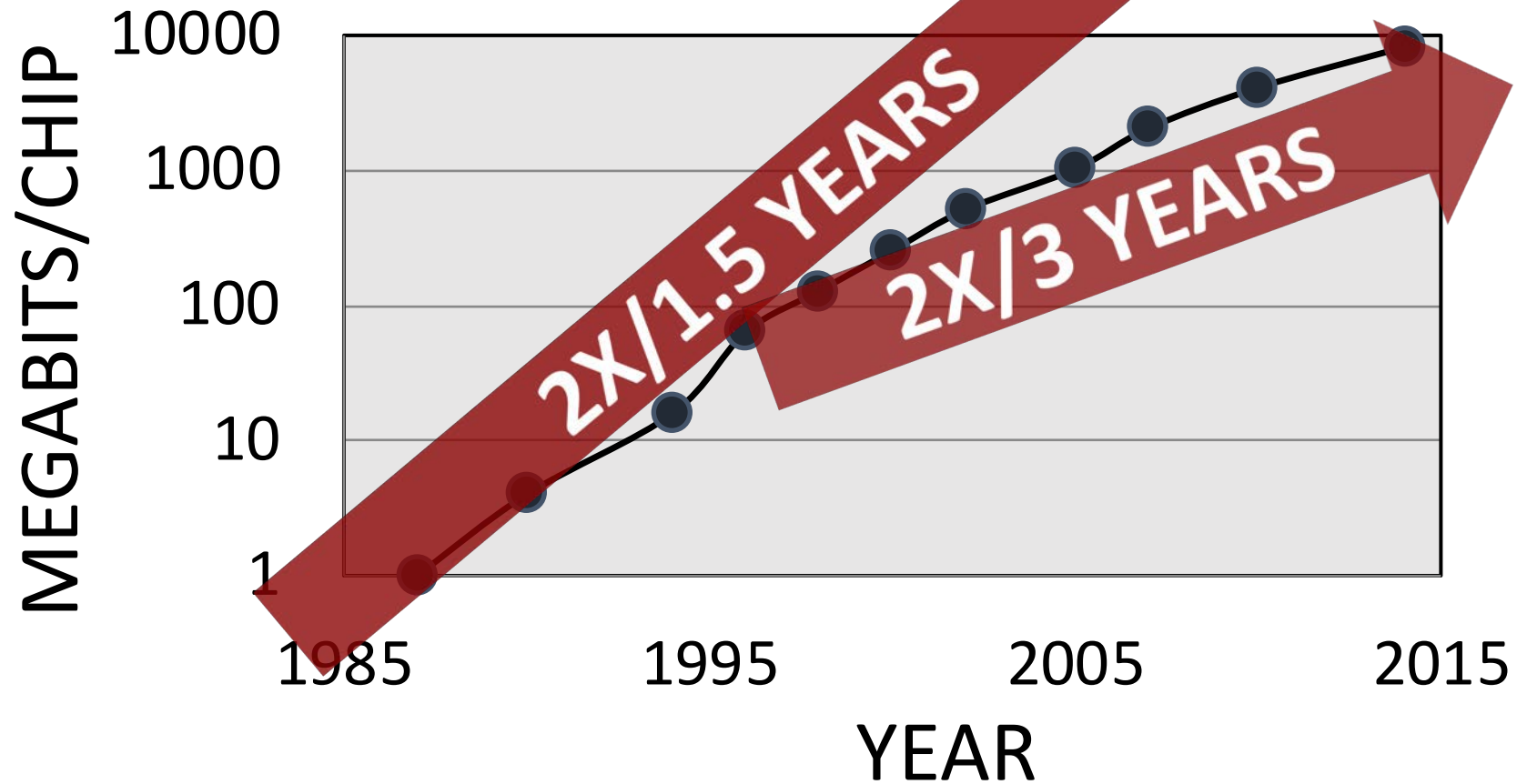
VIRTUAL
REALITY

Spark amazon DynamoDB SAP HANA

IN-MEMORY FRAMEWORKS

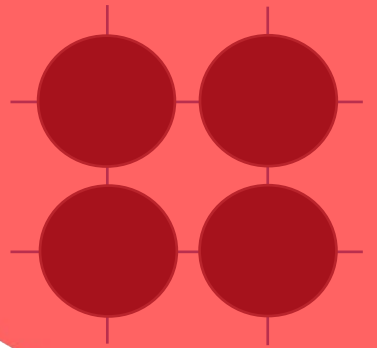
Increasing demand for high-capacity, high-performance, energy-efficient main memory

DRAM SCALING TREND



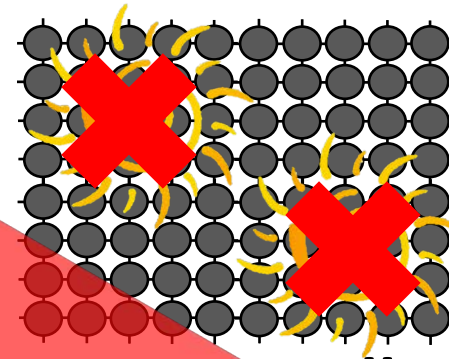
DRAM scaling is getting difficult

DRAM SCALING CHALLENGE



DRAM Cells

Technology
Scaling

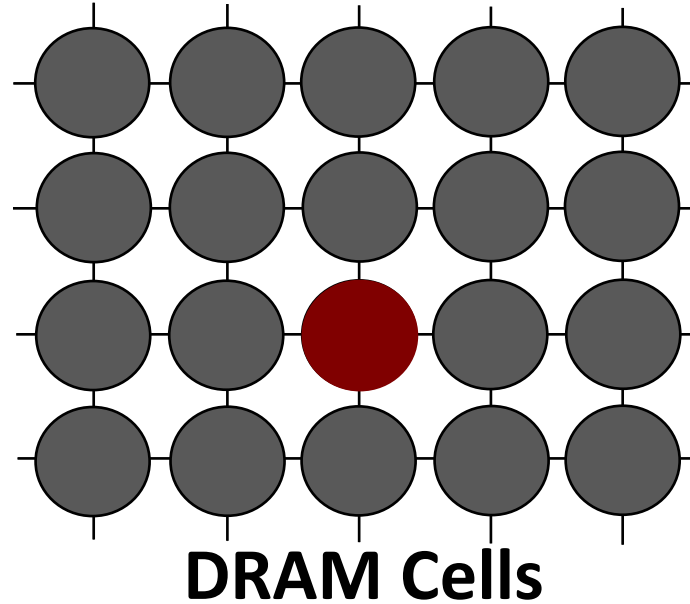


DRAM Cells

WHY?

Manufacturing reliable cells at low cost
is getting difficult

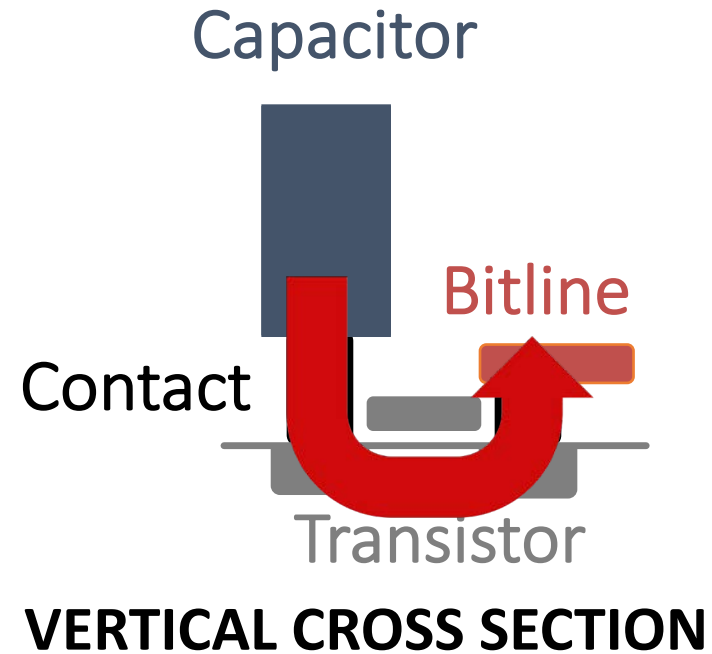
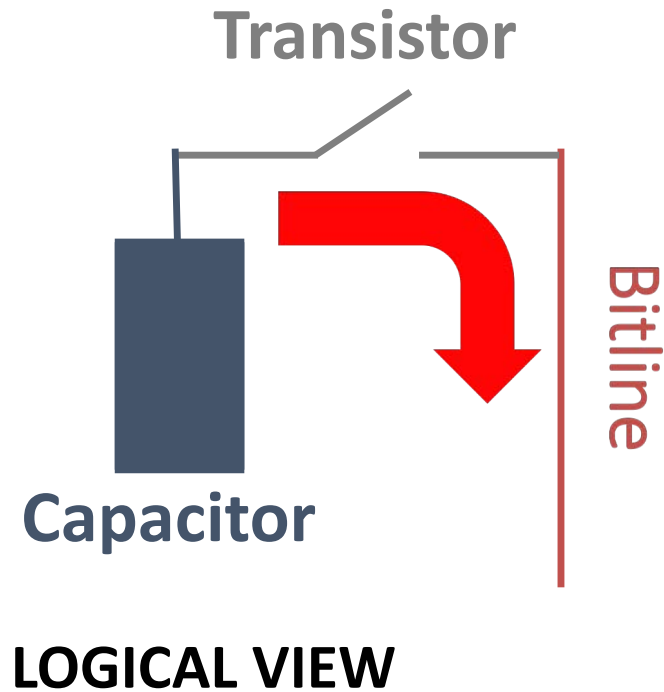
WHY IS IT DIFFICULT TO SCALE?



In order to answer this we need to take a closer look to a DRAM cell

DRAM CELL OPERATION

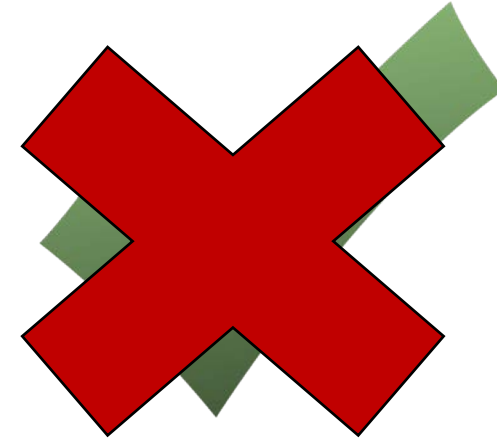
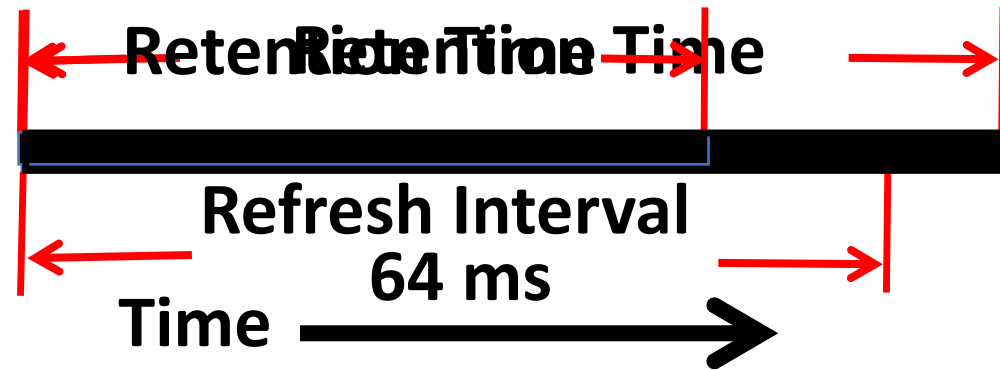
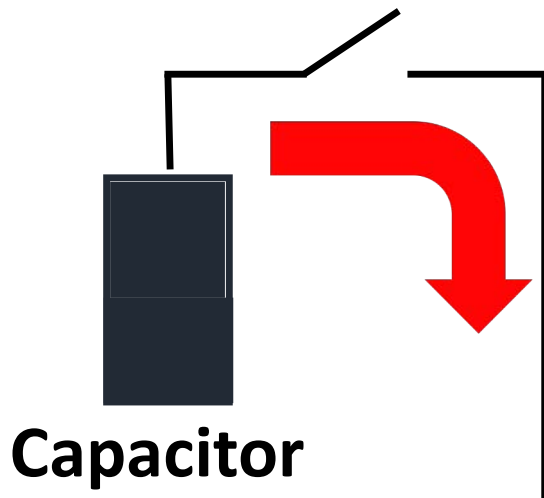
1. A DRAM cell stores **data** as *charge*
2. A DRAM cell is **refreshed** every *64 ms*



A DRAM cell

DRAM RETENTION FAILURE

Retention time: The time when we can still access a cell reliably
Cells need to be refreshed before that to avoid failure

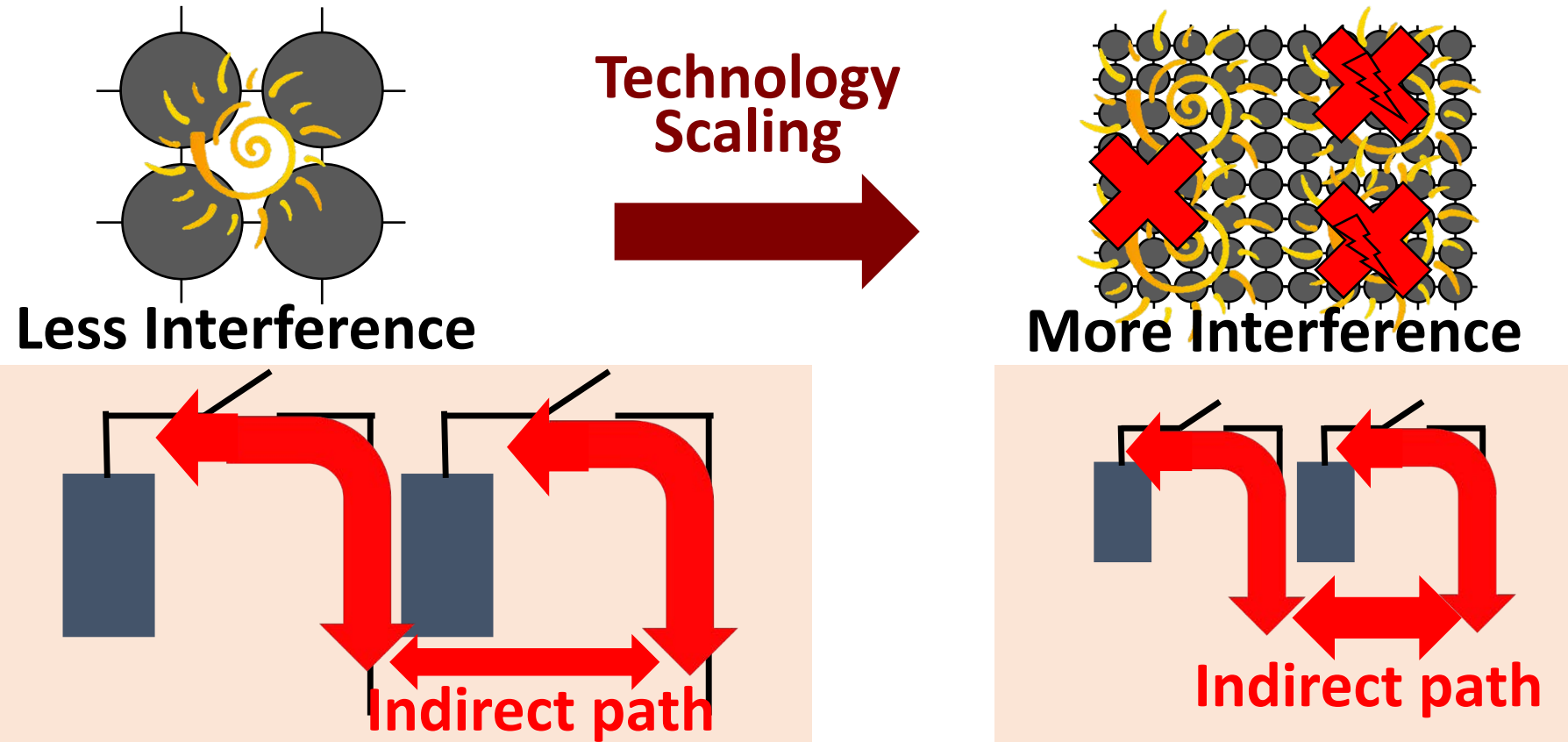


Retention time is
less than refresh interval

Failure depends on the amount of charge

SCALING CHALLENGE: CELL-TO-CELL INTERFERENCE

Cell-to-cell interference affects the charge in neighboring cells



More interference results in more failures

IMPLICATION: DRAM ERRORS IN THE FIELD

DRAM Errors in the Wild: A Large-Scale Field Study

1.52% of DRAM modules failed in Google Servers

A Study of DRAM Failures in the Field

1.6% of DRAM modules failed in LANL

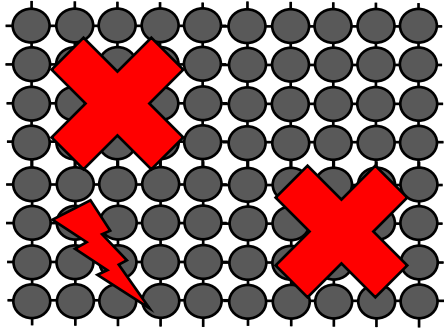
Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field

1.8X more failures in new generation DRAMs in Facebook

GOAL

*Enable
high-capacity, low-latency memory
without
sacrificing reliability*

Traditional DRAM Scaling is Ending

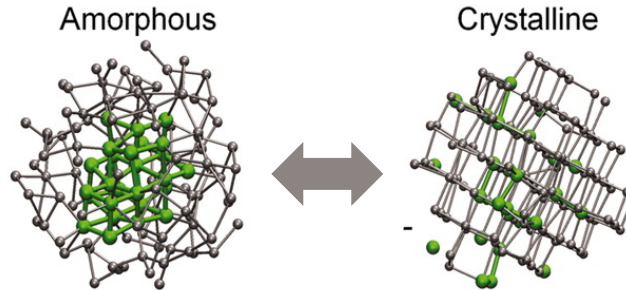


MEMORY

Difficult to scale

**MAKE DRAM
SCALABLE**

SIGMETRICS'14, DSN'15, HPCA'15,
SIGMETRICS'16, DSN'16, CAL'16,
SIGMETRICS'17, HPCA'17, MICRO'17

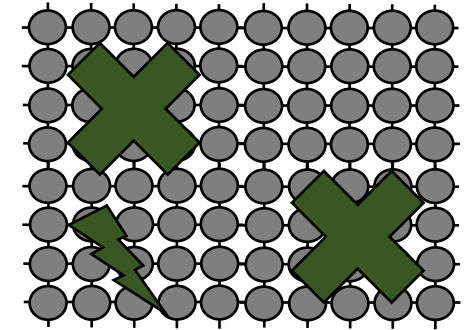


NON-VOLATILE MEMORY

Highly scalable

**LEVERAGE NEW
TECHNOLOGIES**

WEED'13, MICRO'15, HPCA'18,
ONGOING



MEMORY

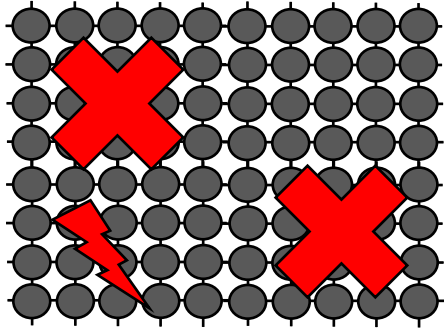
Difficult to scale

**TOLERATE
FAILURES**

WAX'18, ONGOING

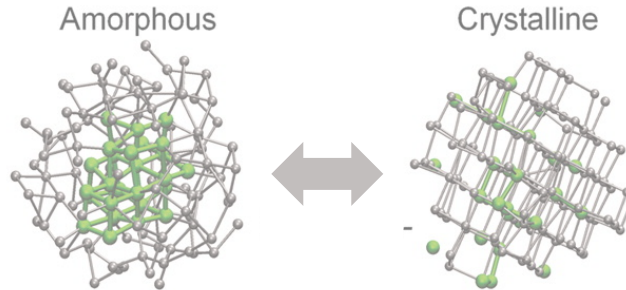
Solution Space

Traditional DRAM Scaling is Ending



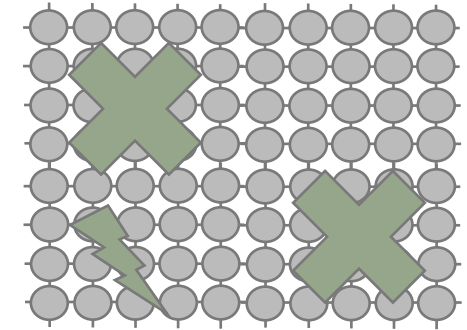
MEMORY
MAKE DRAM
SCALABLE

System-Level
Detection and
Mitigation of
Failures



NON-VOLATILE MEMORY
LEVERAGE NEW
TECHNOLOGIES

Unifying Memory
and Storage
with NVM

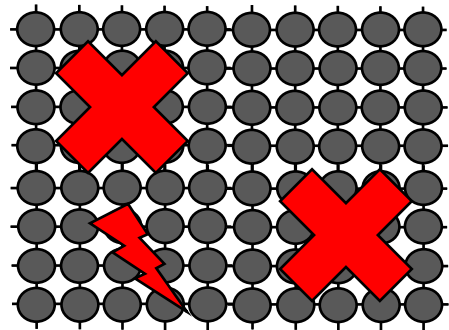


MEMORY
TOLERATE
FAILURES

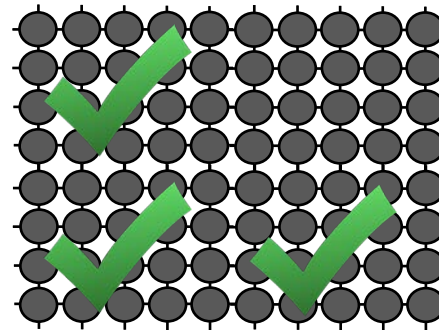
Restricted
Approximation

Solution Space

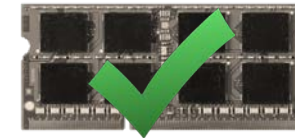
TRADITIONAL APPROACH TO ENABLE DRAM SCALING



**Unreliable
DRAM Cells**



**Reliable
DRAM Cells**



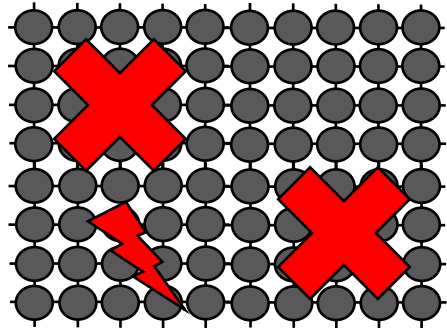
Reliable System

Manufacturing Time

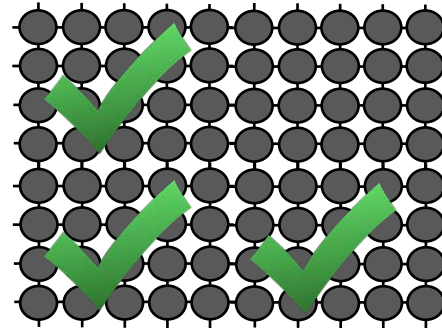
**System
in the Field**

DRAM has strict reliability guarantee

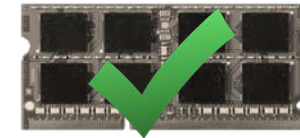
MY APPROACH



**Unreliable
DRAM Cells**



**Reliable
DRAM Cells**



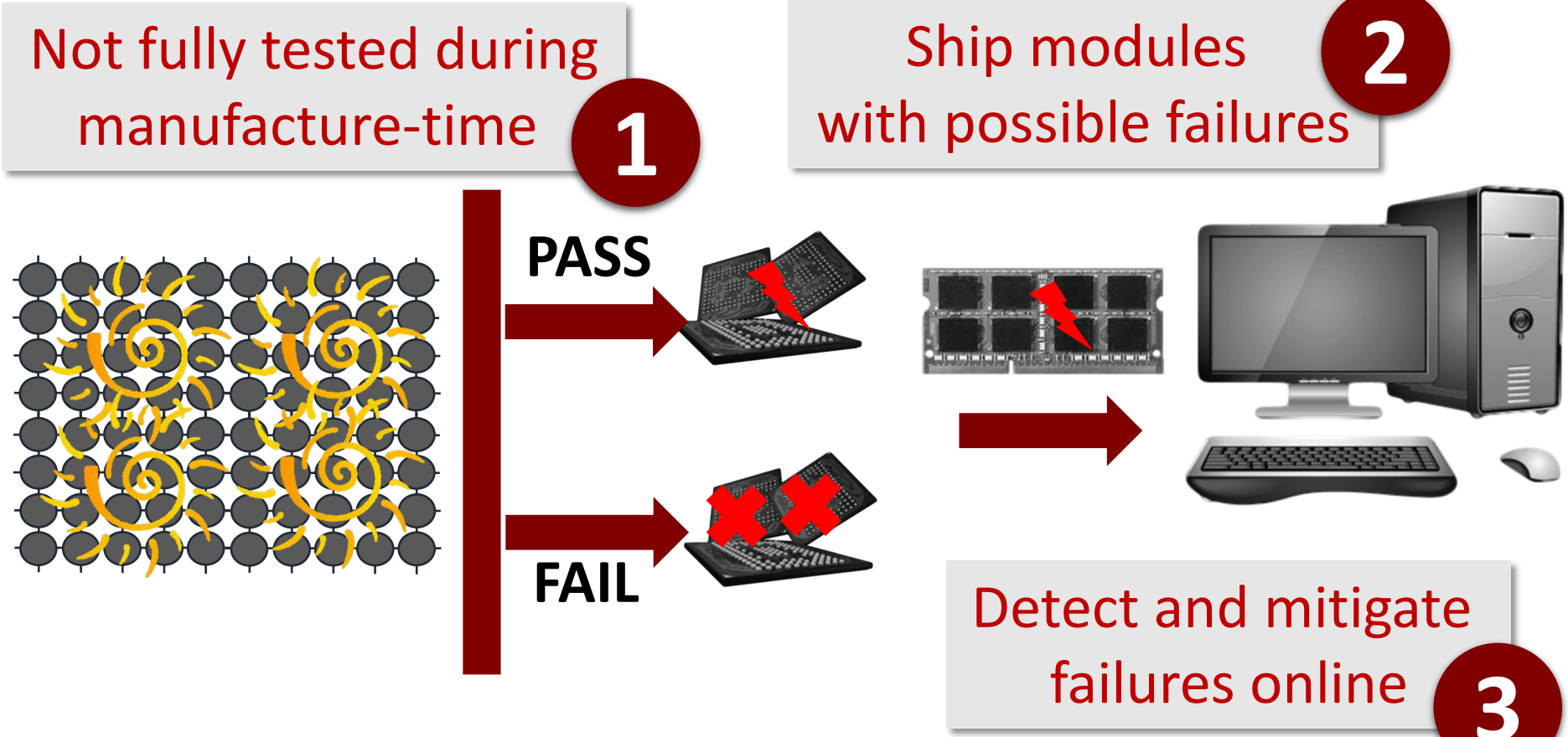
Reliable System

**Manufacturing
Time**

**System
in the Field**

Shift the responsibility to systems

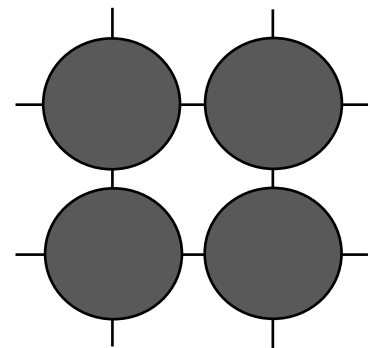
VISION: SYSTEM-LEVEL DETECTION AND MITIGATION



Detect and mitigate errors after the system has become operational

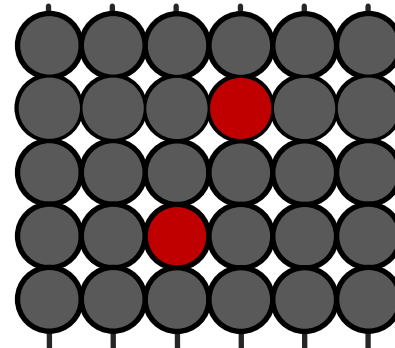
ONLINE PROFILING

BENEFITS OF ONLINE PROFILING



**Reliable
DRAM Cells**

**Technology
Scaling**



**Unreliable
DRAM Cells**

1. Improves yield, reduces cost, enables scaling

Vendors can make cells smaller without a strong reliability guarantee

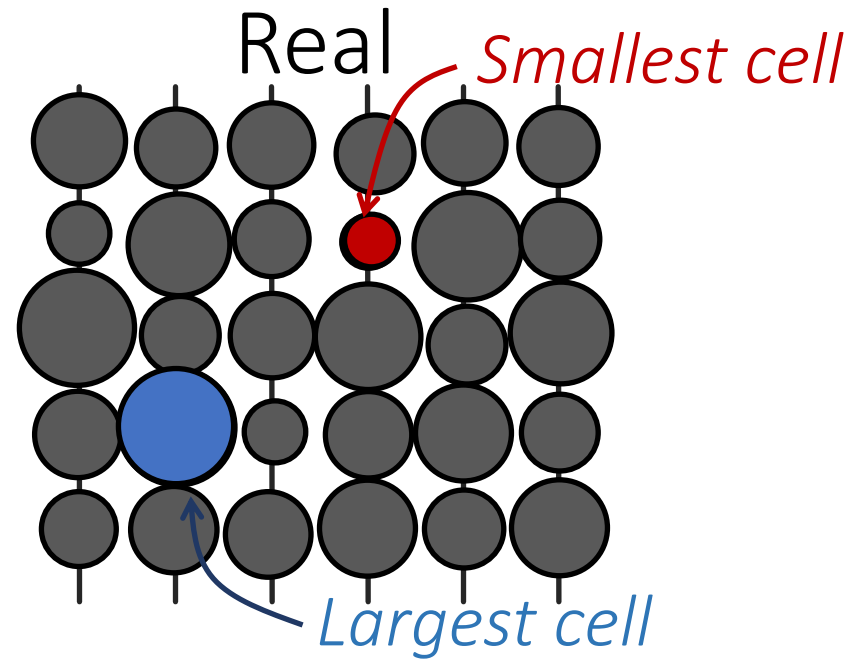
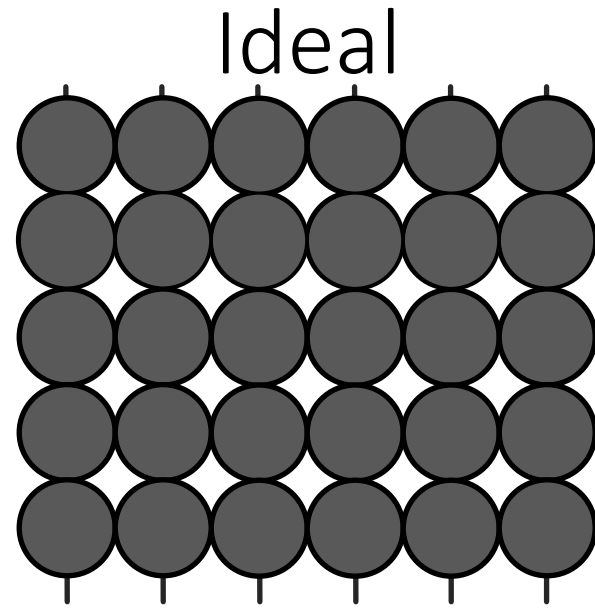
BENEFITS OF ONLINE PROFILING



1. Improves yield, reduces cost, enables scaling
Vendors can make cells smaller without a strong reliability guarantee

2. Improves performance and energy efficiency

DRAM CELLS ARE NOT EQUAL

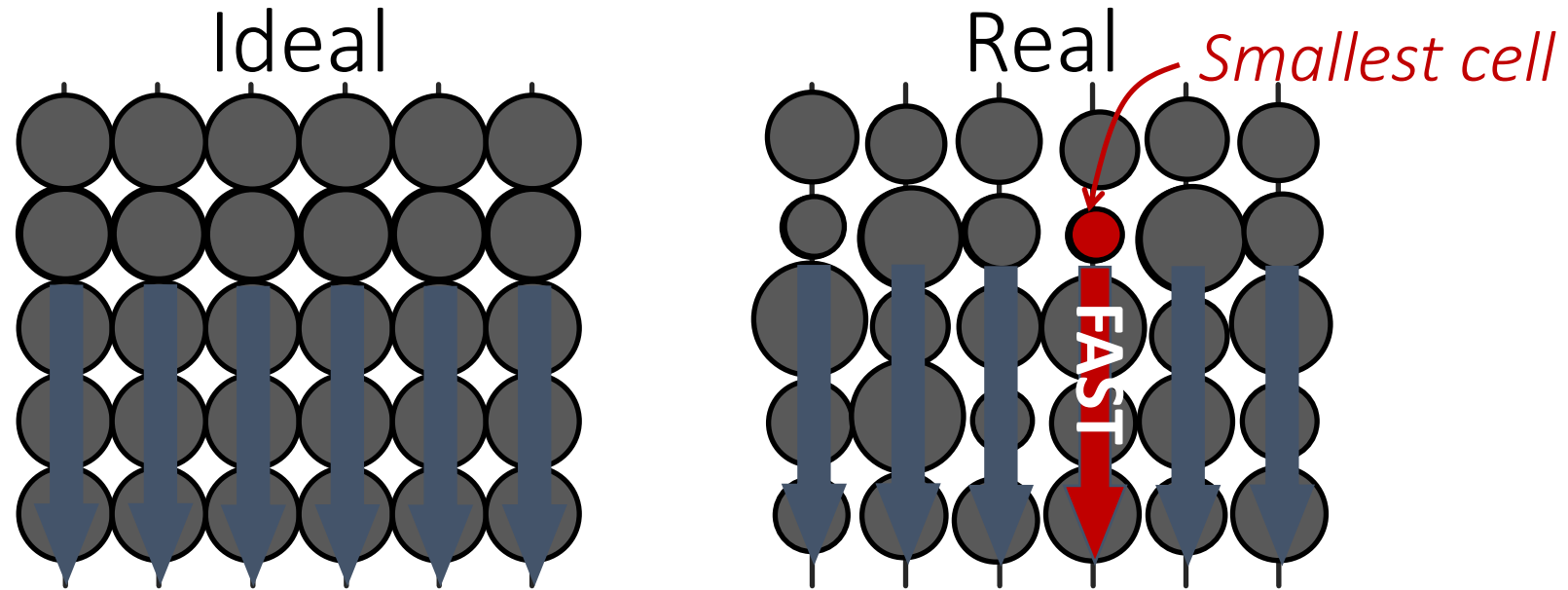


Same size →
Same charge →

Different size →
Different charge →

Large variation in DRAM cells

DRAM CELLS ARE NOT EQUAL

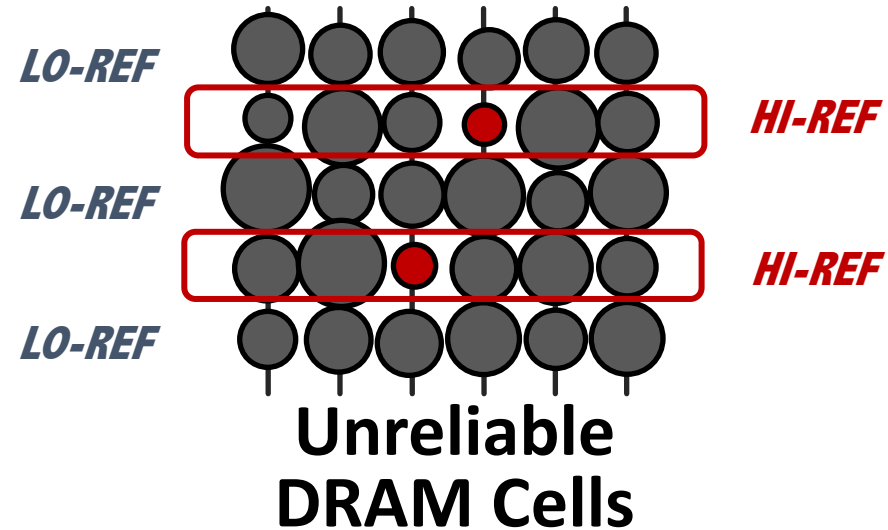


Large variation in retention time

Most cells have high retention time →
can be refreshed at a lower rate without any failure

Smaller cells will fail to retain data at a lower refresh rate

BENEFITS OF ONLINE PROFILING



Reduce refresh count by using a lower refresh rate, but use higher refresh rate for faulty cells

1. Improves yield, reduces cost, enables scaling

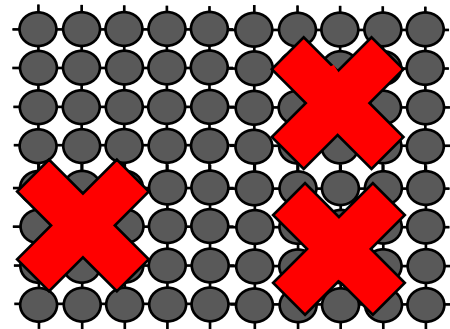
Vendors can make cells smaller without a strong reliability guarantee

2. Improves performance and energy efficiency

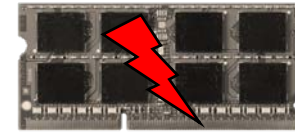
Reduce refresh rate, refresh faulty rows more frequently

*In order to enable these benefits,
we need to **detect** the **failures**
at the system level*

CHALLENGE: INTERMITTENT FAILURES



Unreliable
DRAM Cells



Reliable System

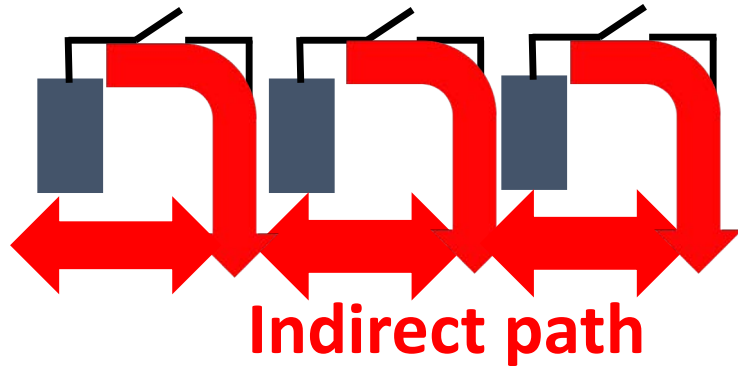
Depends on accurately *detecting* DRAM failures

If failures were permanent,
a simple boot up test would have worked,

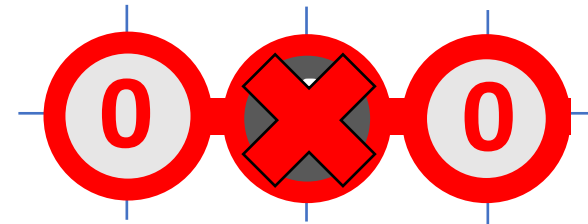
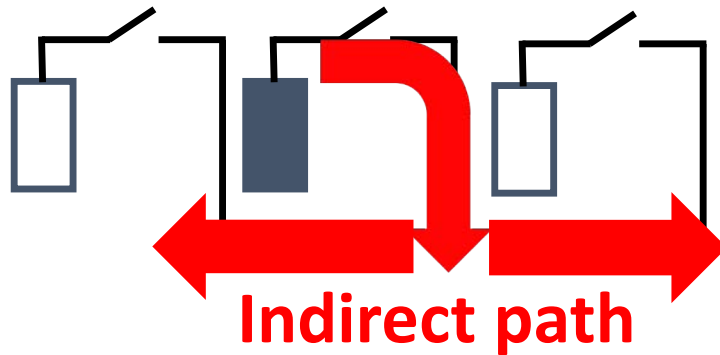
but there are intermittent failures

What are the these intermittent failures?

CELL-TO-CELL INTERFERENCE: DATA-DEPENDENT FAILURES



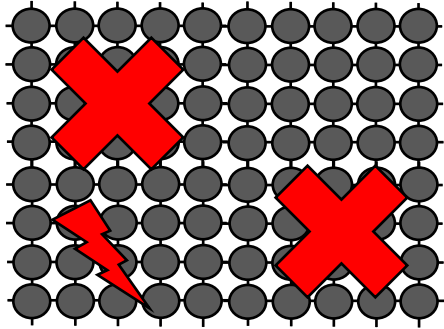
*NO
FAILURE*



FAILURE

Some cells can fail depending on the data stored in neighboring cells

How to detect these failures at the system?



DRAM

**MAKE DRAM
SCALABLE**

**System-Level
Detection and
Mitigation of
Failures**

**CHALLENGE:
Data-Dependent Failures**

**Efficacy of Testing
Data-Dependent Failures**

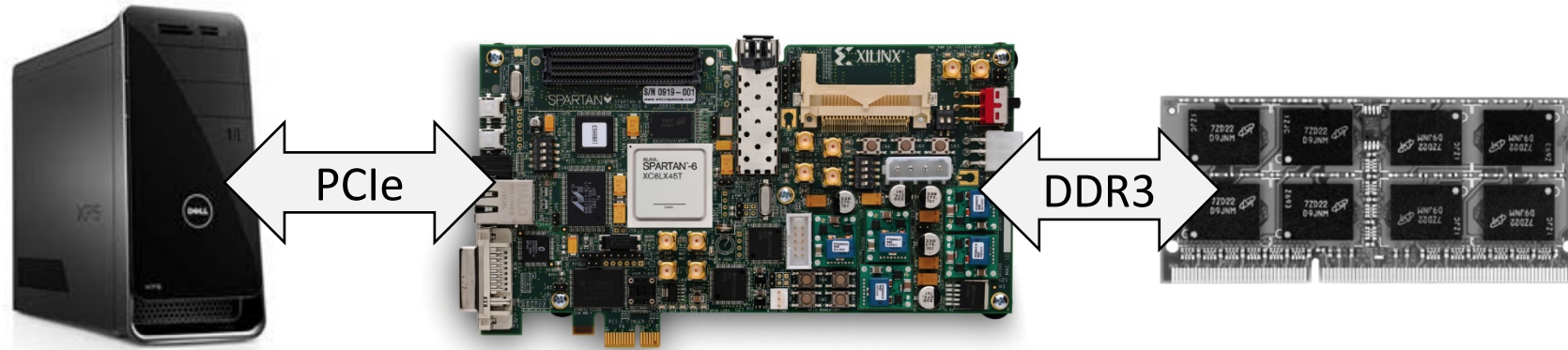
SIGMETRICS'14

**MEMCON: DRAM-Internal
Independent Detection**

CAL'16, MICRO'17

Experimental Methodology

Custom FPGA-based infrastructure



PC

C++ programs to
specify commands

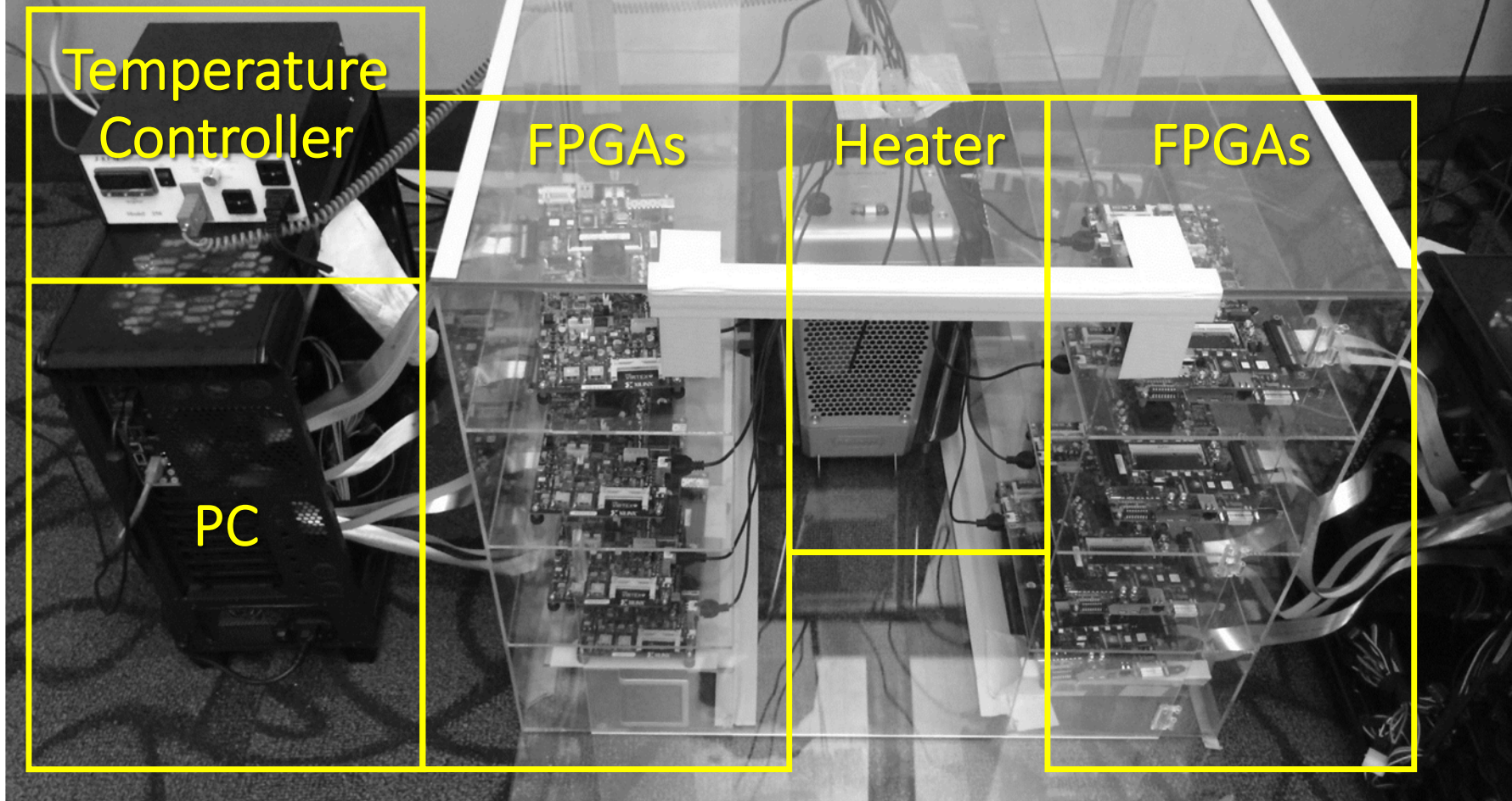
FPGA

Generate
command sequence

DIMM

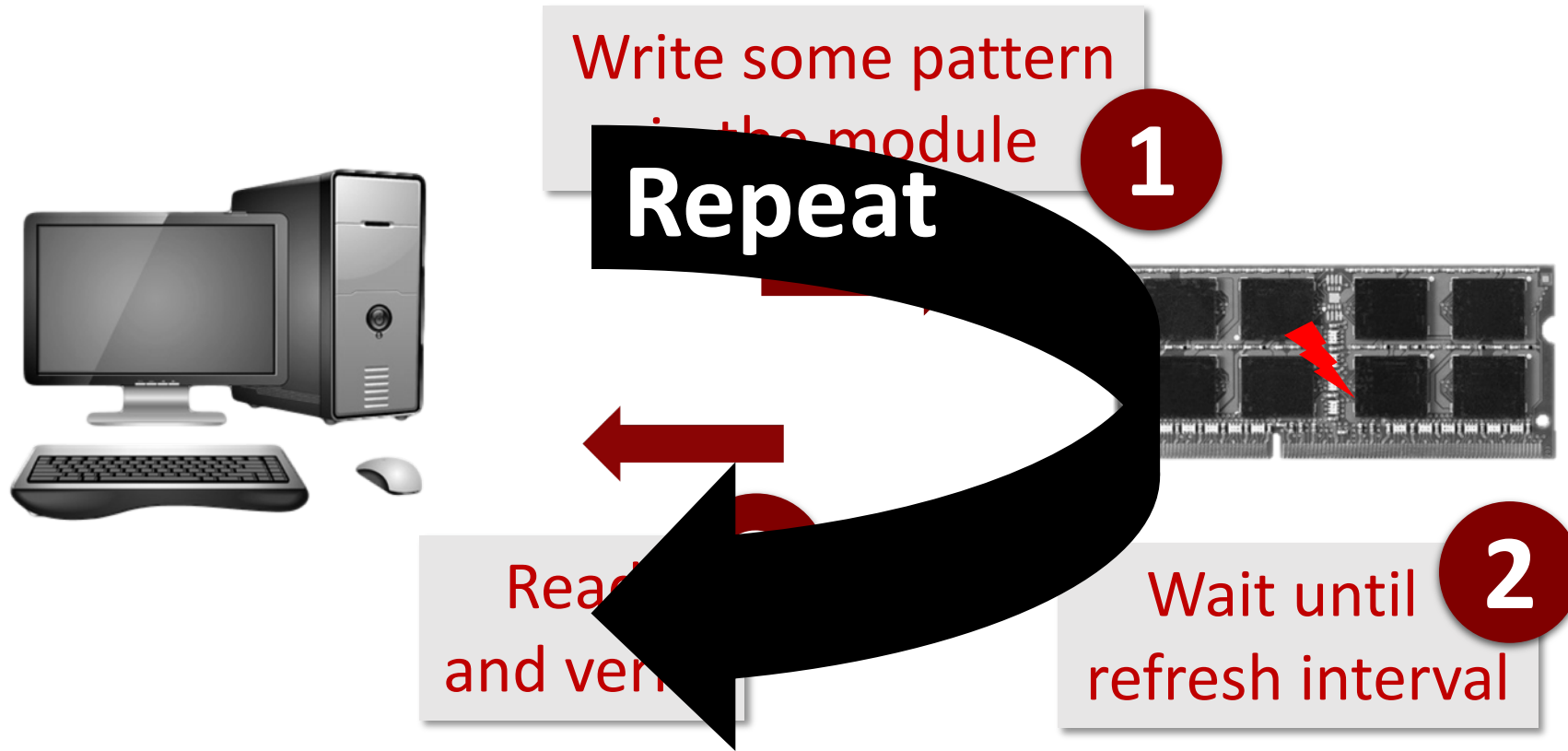
**Tested more than hundred chips from
three different manufacturers**

DRAM Testing Infrastructure



Open-source infrastructure to test real DRAM chips
Characterization data publicly available

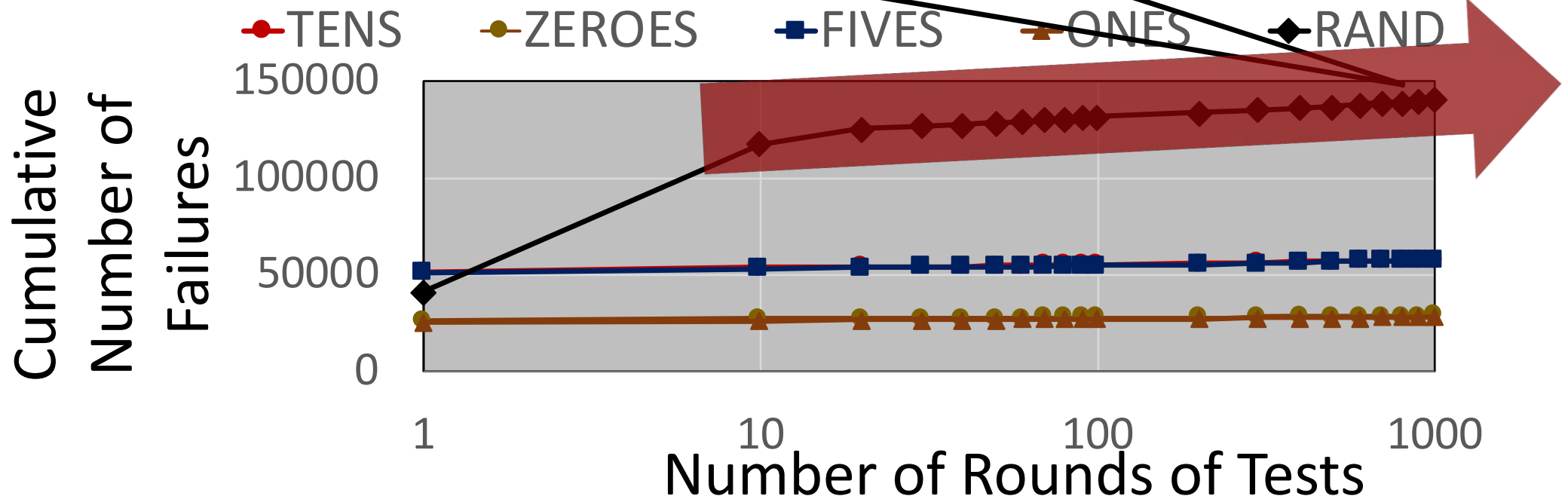
DETECT FAILURES WITH TESTING



Test with different data patterns

DETECTING DATA-DEPENDENT FAILURES

Even after hundreds of rounds,
a small number of new cells keep failing

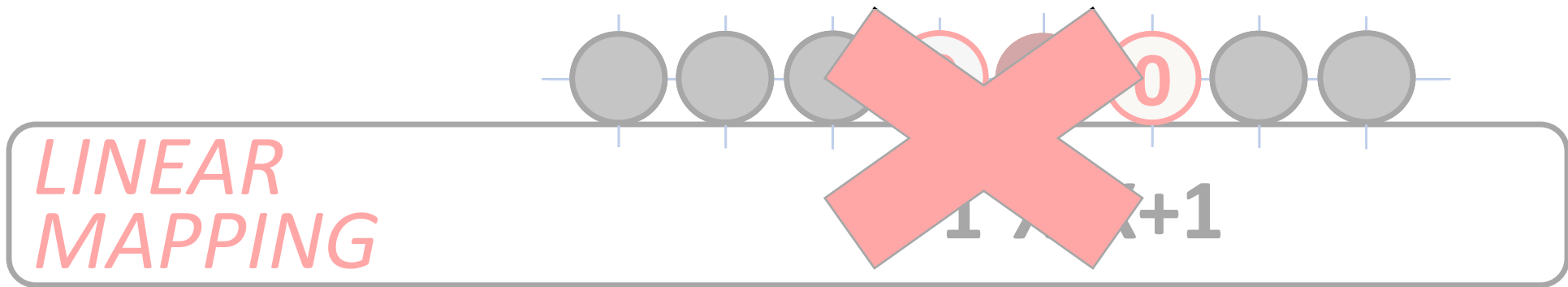


Conclusion: Tests with many rounds of random patterns
cannot *detect* all failures

WHY SO MANY ROUNDS OF TESTS?

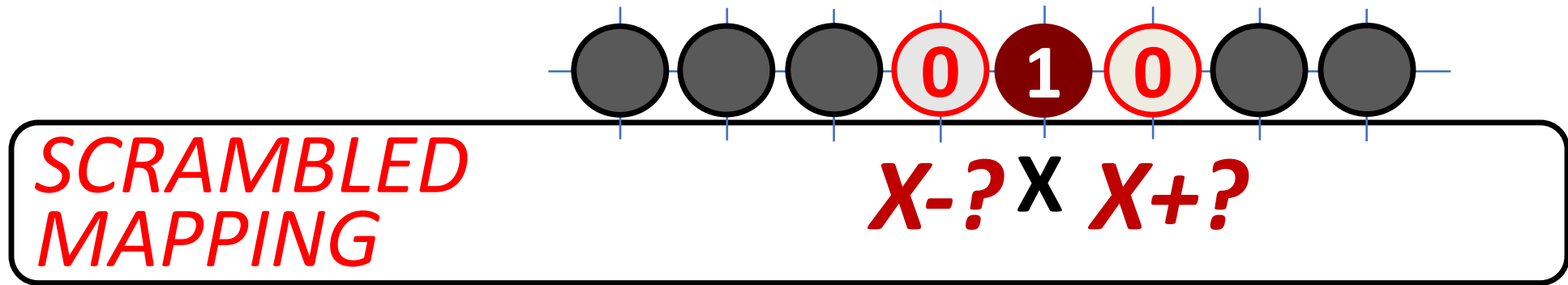
DATA-DEPENDENT FAILURE

Fails when specific pattern in the neighboring cell

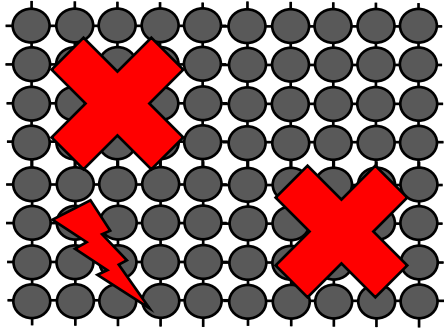


Even many rounds of random patterns cannot detect all failures

CHALLENGE IN DETECTION



How to detect *data-dependent failures*
when we even do not know
which *cells are neighbors*?



DRAM

**MAKE DRAM
SCALABLE**

**System-Level
Detection and
Mitigation of
Failures**

**CHALLENGE:
Data-Dependent Failures**

**Efficacy of Testing
Data-Dependent Failure**

SIGMETRICS'14

**MEMCON: DRAM-Internal
Independent Detection**

CAL'16, MICRO'17

CURRENT DETECTION MECHANISM

Initial Failure Detection and Mitigation

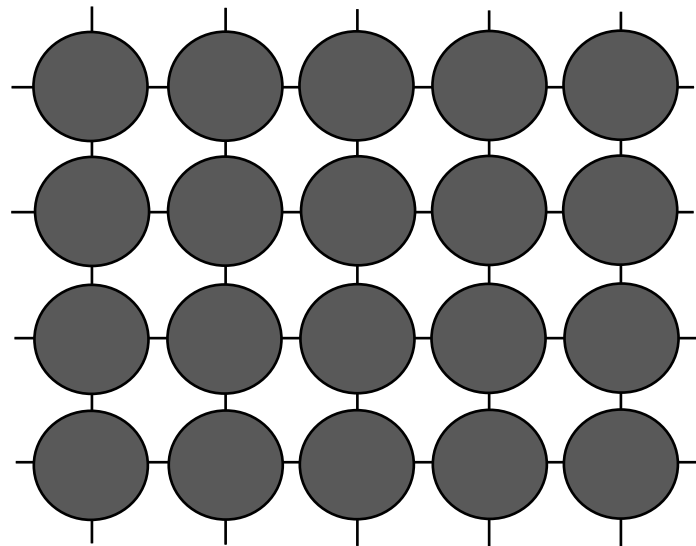
Execution
of Applications

Detection is done with some initial testing
isolated from system execution

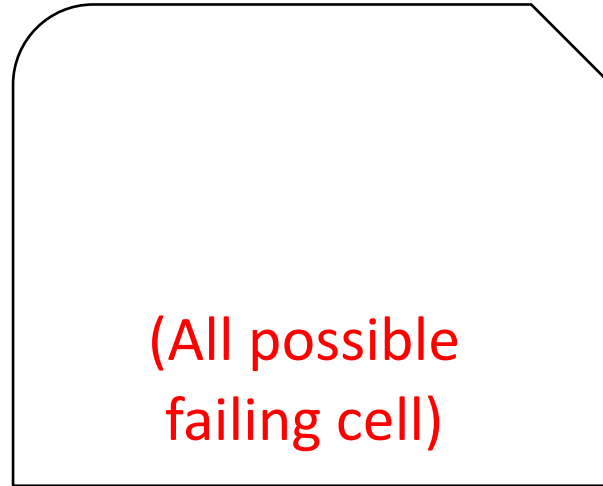
1. Detect and mitigate all failures with every possible content
2. Only after that start program execution

CURRENT DETECTION MECHANISM

Detect every possible failure with all content before execution



Unreliable
DRAM Cells



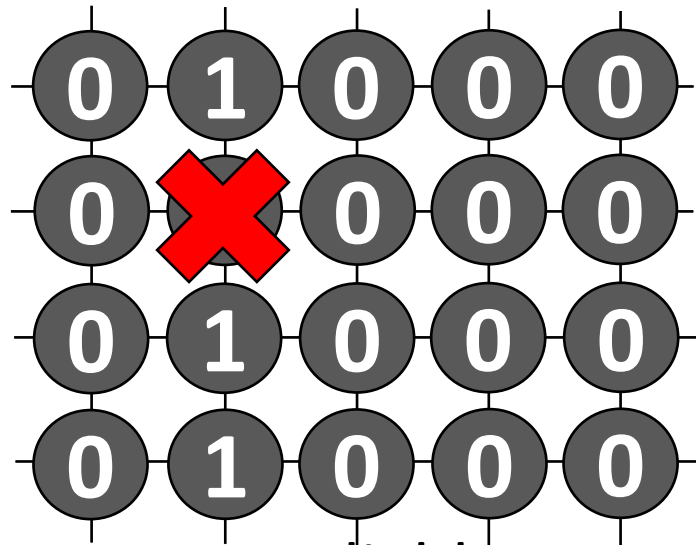
(All possible
failing cell)

List of Failures

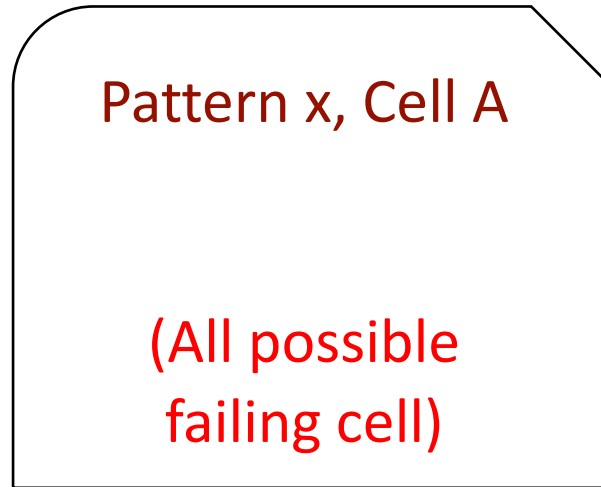
Initial Failure Detection and Mitigation

CURRENT DETECTION MECHANISM

Detect every possible failure with all content before execution



Unreliable
DRAM Cells

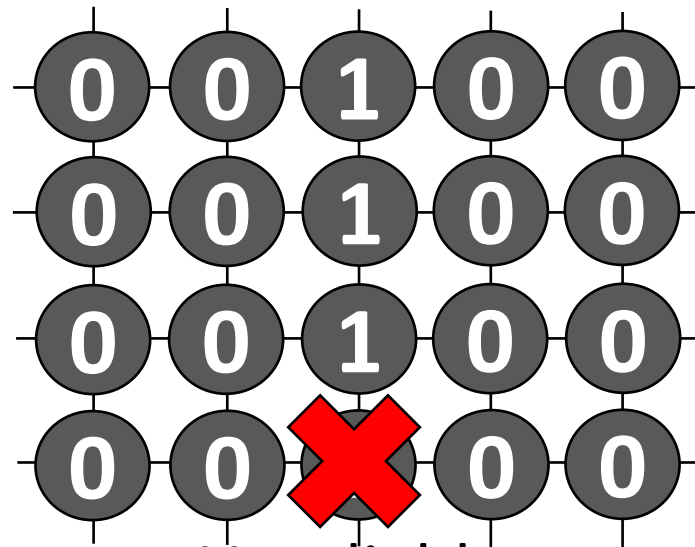


List of Failures

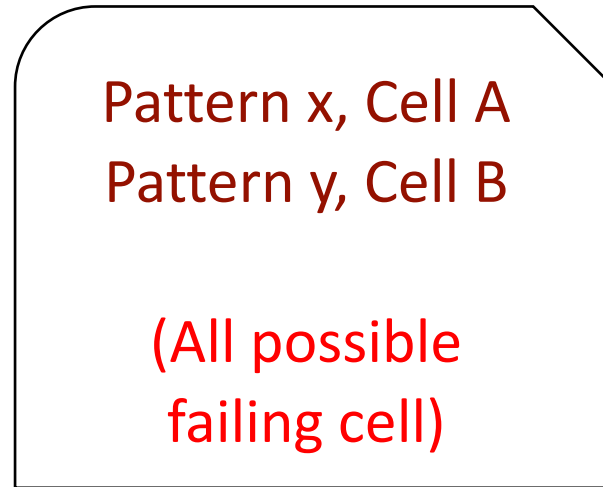
Initial Failure Detection and Mitigation

CURRENT DETECTION MECHANISM

Detect every possible failure with all content before execution



Unreliable
DRAM Cells

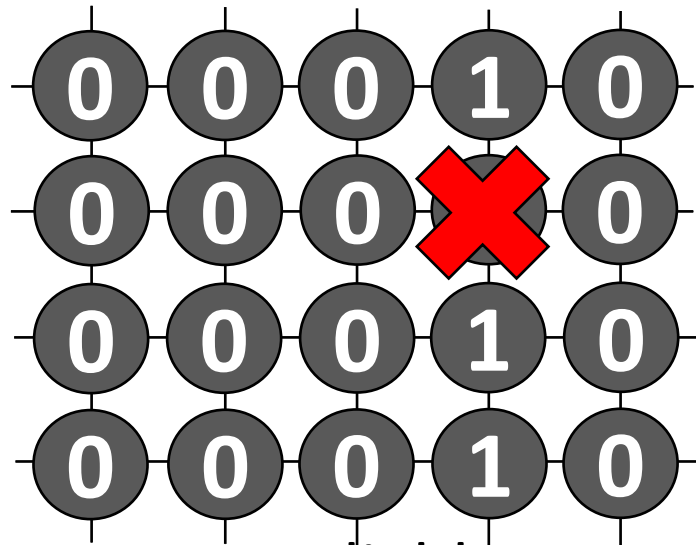


List of Failures

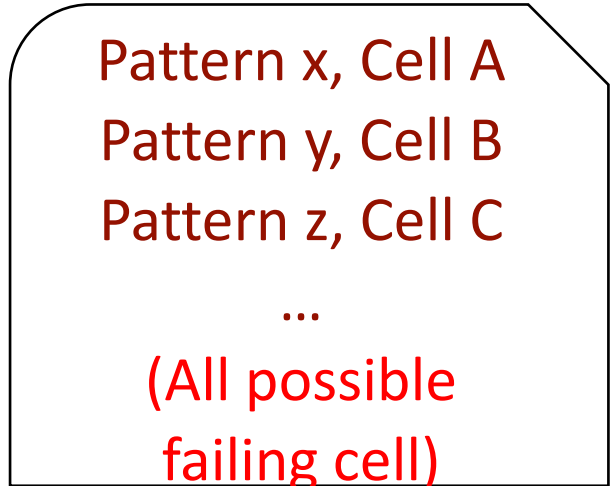
Initial Failure Detection and Mitigation

CURRENT DETECTION MECHANISM

Detect every possible failure with all content before execution



Unreliable
DRAM Cells



List of Failures



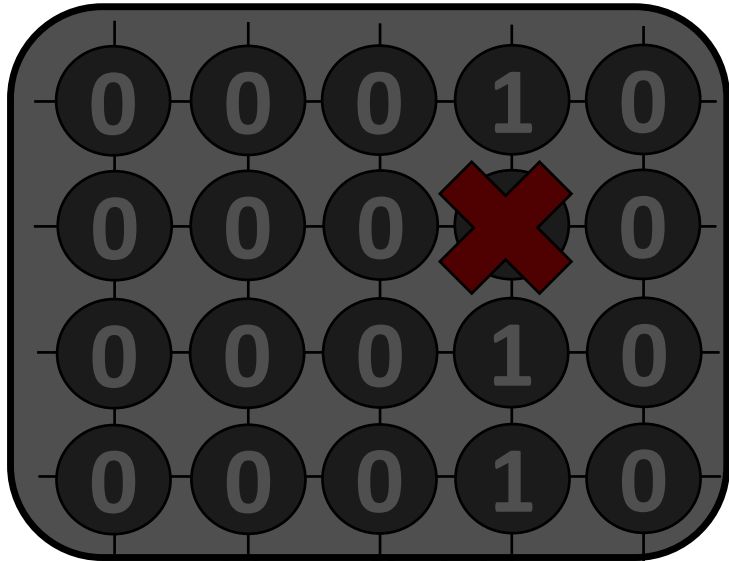
Applications

Initial Failure Detection and Mitigation

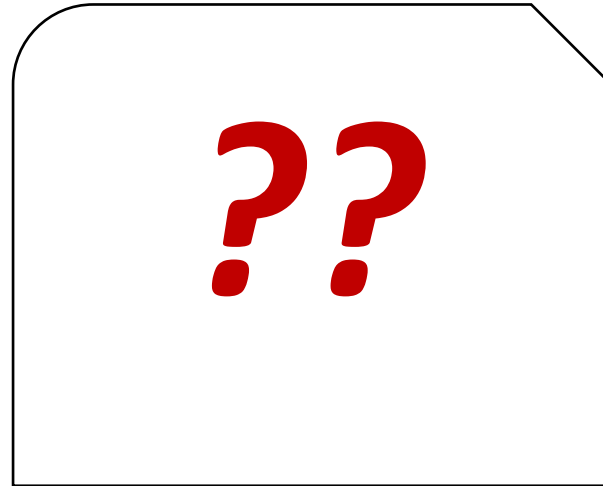
Execution
of Applications

CURRENT DETECTION MECHANISM

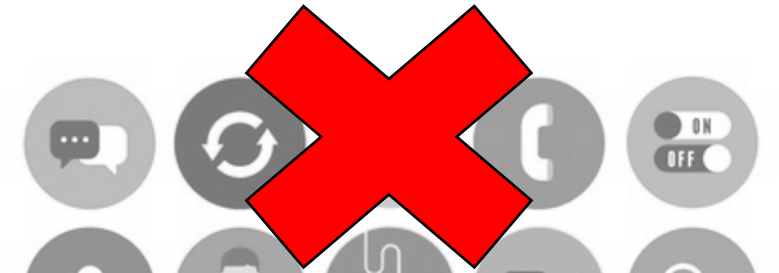
Detect every possible failure with all content before execution



Unreliable
DRAM Cells



List of Failures



No Reliability
Guarantee

Applications

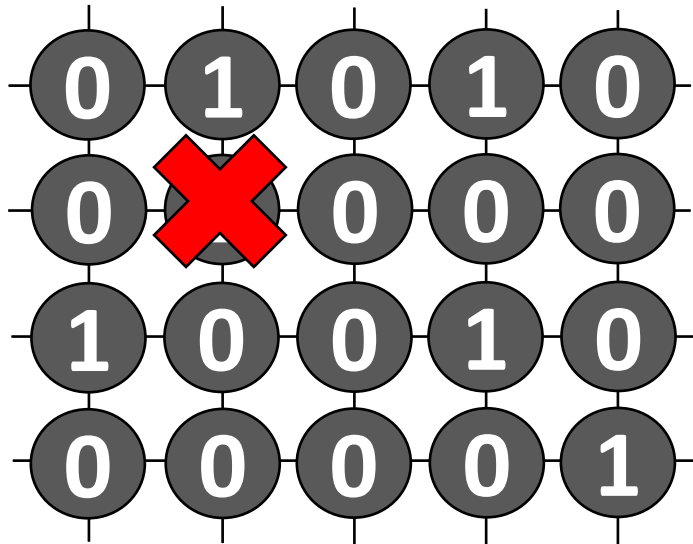
Execution
of Applications

Initial Failure Detection and Mitigation

Online profiling cannot detect *all* failures
as the address mapping is not visible to the system

MEMCON: MEMORY CONTENT-BASED DETECTION AND MITIGATION

NO NEED TO DETECT EVERY POSSIBLE FAILURE



Unreliable DRAM Cells
with Program Content

Current content,
Cell A

List of Failures



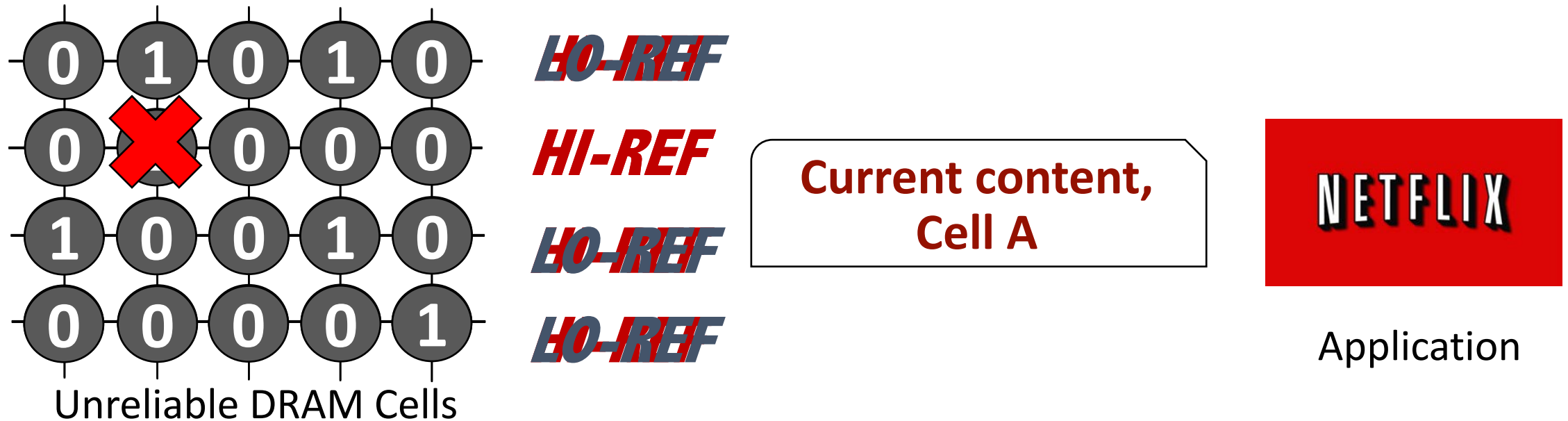
Application

**Simultaneous Detection and Execution
Based on current memory content of running applications**

**Need to detect and mitigate
only with the current content**

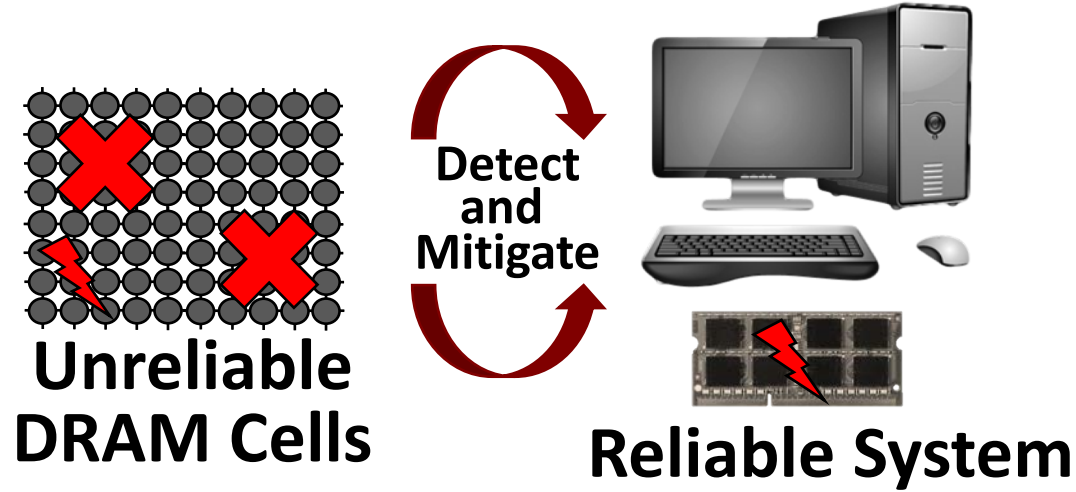
MEMCON: HIGH-LEVEL DESIGN

Simultaneous Detection and Execution



1. No initial detection and mitigation
2. Start running the application with a high refresh rate
3. Detect failures with the current memory content
 - If no failure found, use a low refresh rate

SUMMARY: ONLINE PROFILING



Detection at the system-level is **challenging** due to data-dependent failures

It is possible to ***detect and mitigate*** data-dependent failures ***simultaneously with program execution***

65%-74%

Reduction in
refresh count

40%-50%

Performance
improvement

SOLVING THE DRAM SCALING CHALLENGE

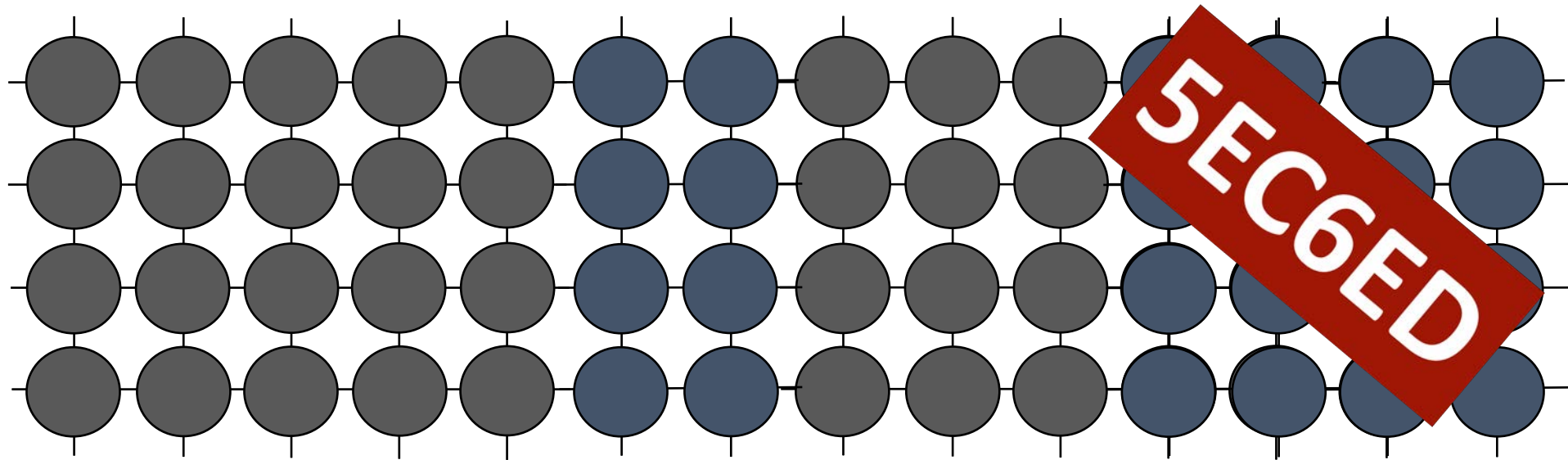
Samira Khan



WHY NOT USE ECC?

No testing, use strong ECC

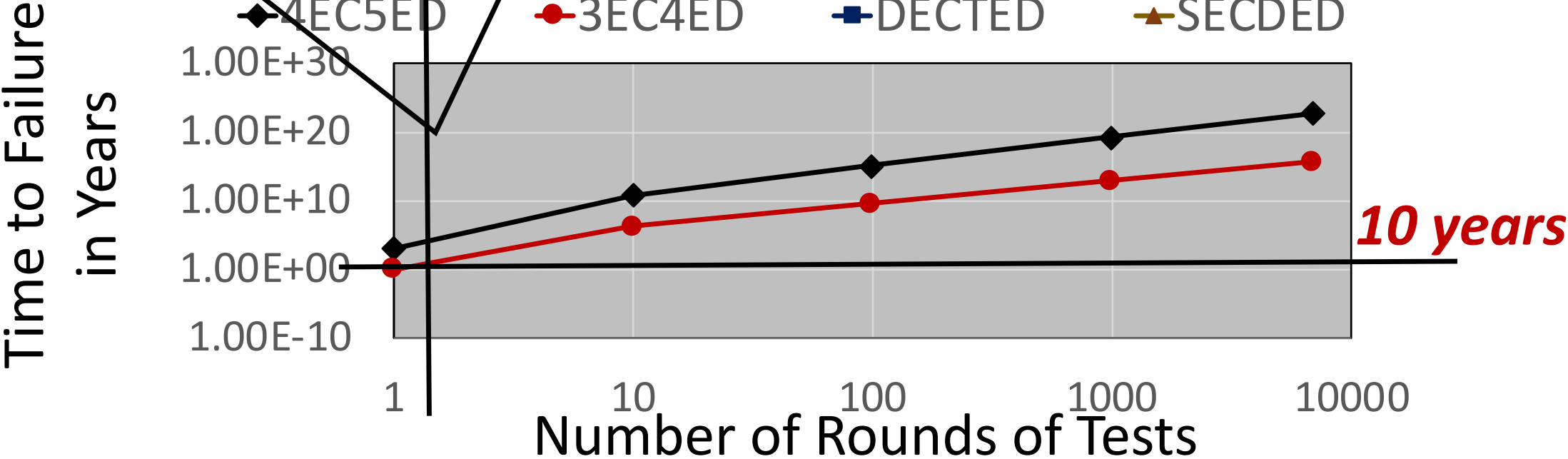
But amortize cost of ECC over larger data chunk



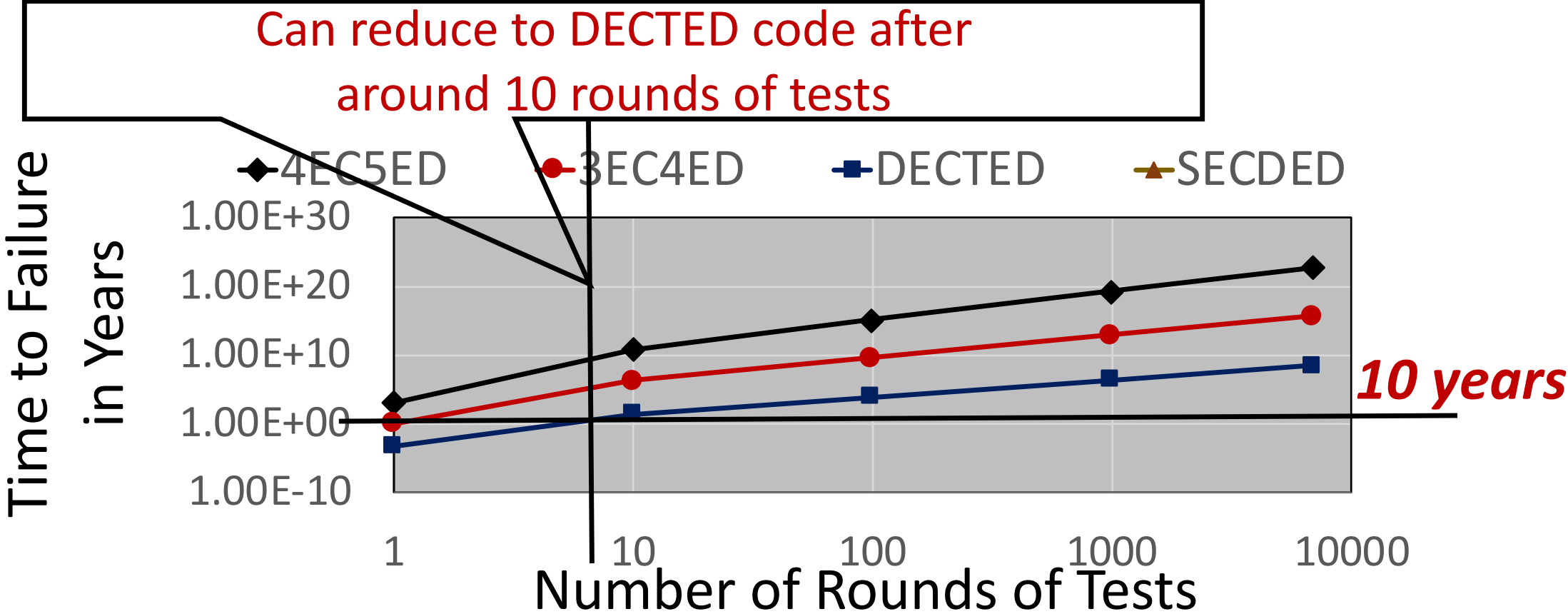
Can potentially tolerate errors
at the cost of higher strength ECC

DETECTING DATA-DEPENDENT FAILURES

After starting with 4EC5ED, can reduce to 3EC4ED code after 2 rounds of tests

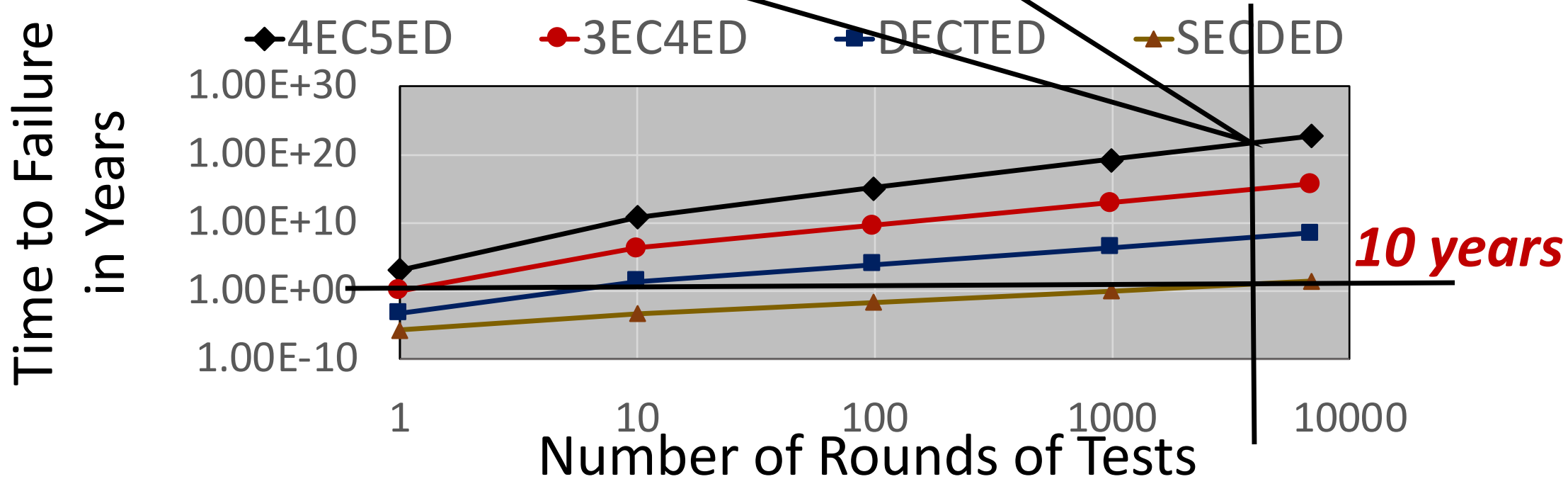


DETECTING DATA-DEPENDENT FAILURES



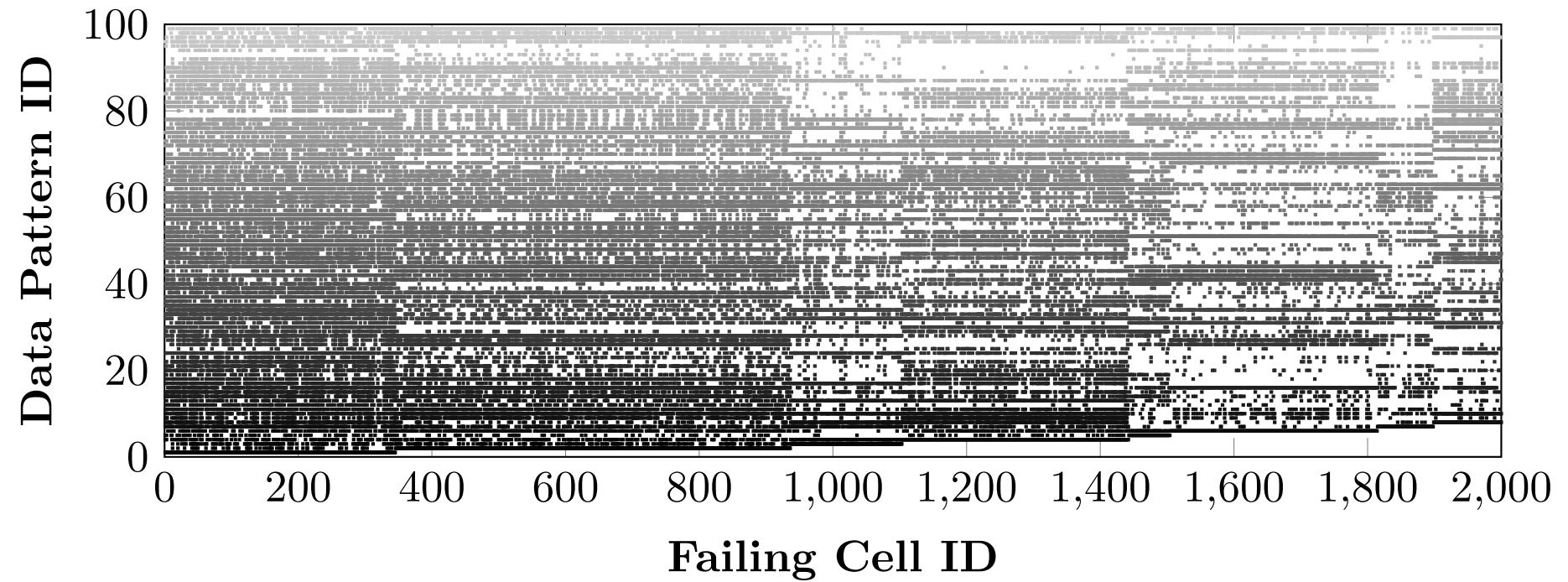
DETECTING DATA-DEPENDENT FAILURES

Can reduce to SECDED code after 7000 rounds of tests (4 hours)



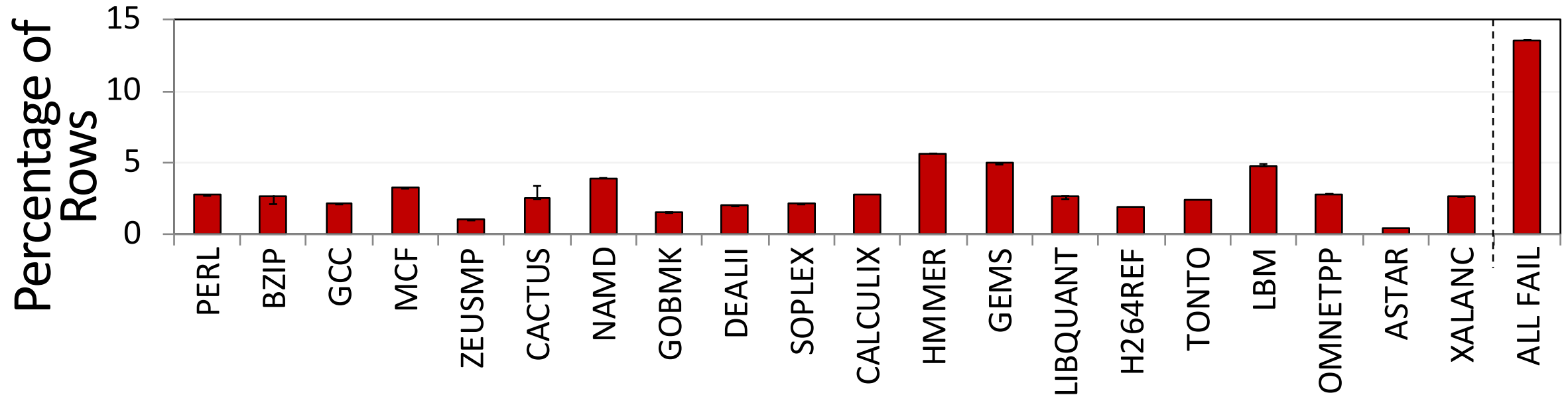
Conclusion: Testing can help to reduce the ECC strength, but *blocks memory for hours*

DATA-DEPENDENT FAILURE



NUMBER OF FAILING ROWS WITH PROGRAM CONTENT

Tested with program content in real DRAM chips

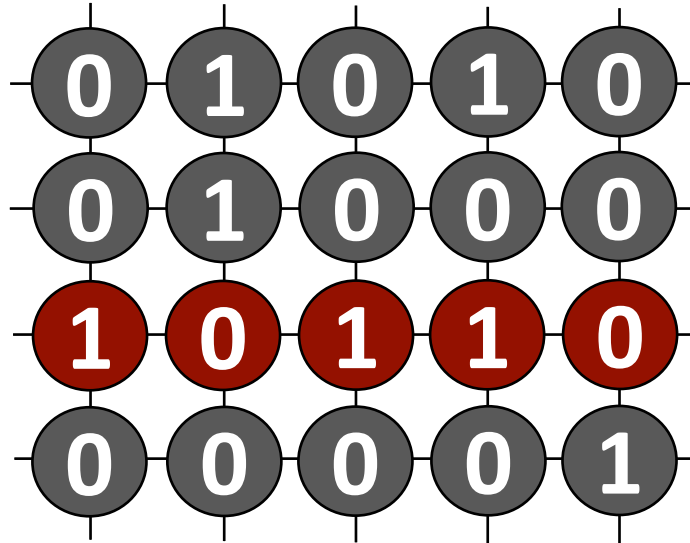


Program content exhibits significantly less failures

CHALLENGE WITH MEMCON

NEED TO DETECT FAILURE AT A WRITE

Write access
to row A



Unreliable DRAM Cells
with Program Content

Current content,
Cell ??

Testing at every write is expensive!!!

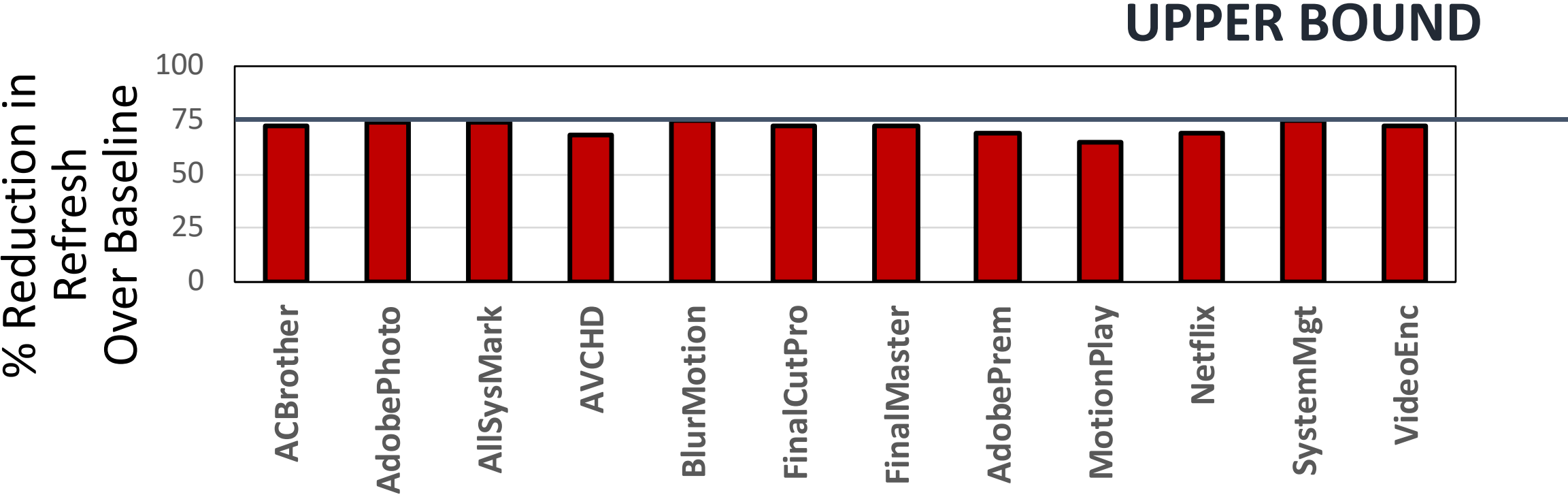
MEMCON: MECHANISM

Does not test at every write



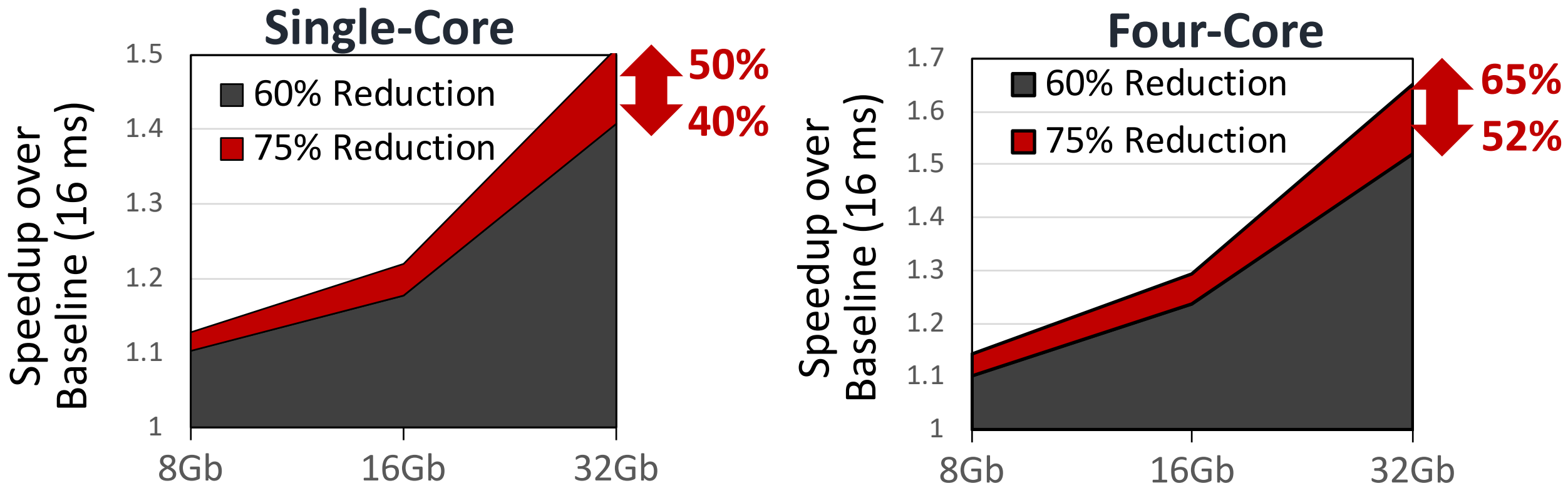
MEMCON *selectively* initiates testing when the write interval is *long enough to amortize* the cost of testing

MEMCON: REDUCTION IN REFRESH COUNT



On average 71% reduction in refresh count, very close to the upper bound of 75%

MEMCON: PERFORMANCE IMPROVEMENT DUE TO REDUCTION IN REFRESH COUNT

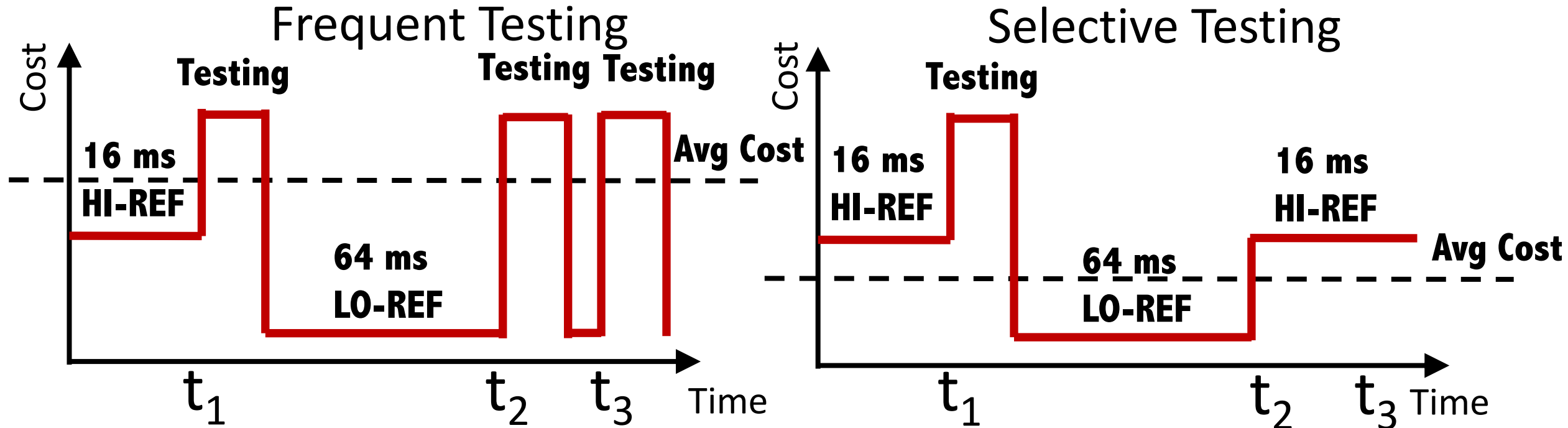


Refresh reduction leads to significant performance improvement

MEMCON: COST-BENEFIT ANALYSIS

Cost: Extra memory accesses to read and write rows

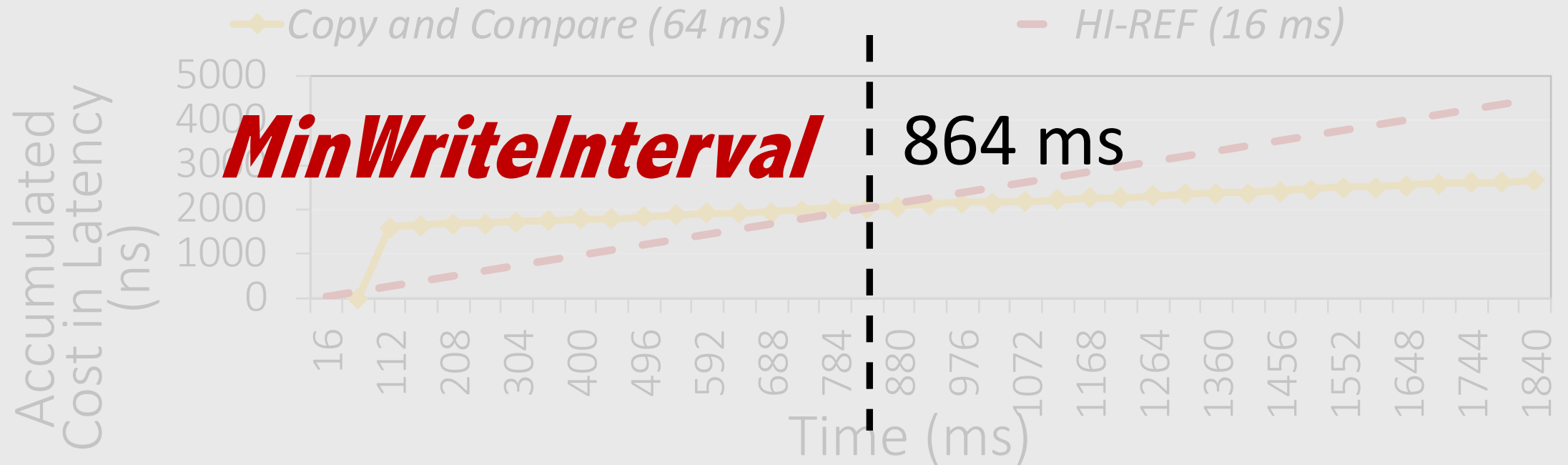
Benefit: If no failure found, can reduce refresh rate



Initiate a test only when the cost can be amortized

MEMCON: COST BENEFIT ANALYSIS

What is the write interval that can amortize the cost?



MEMCON: MECHANISM

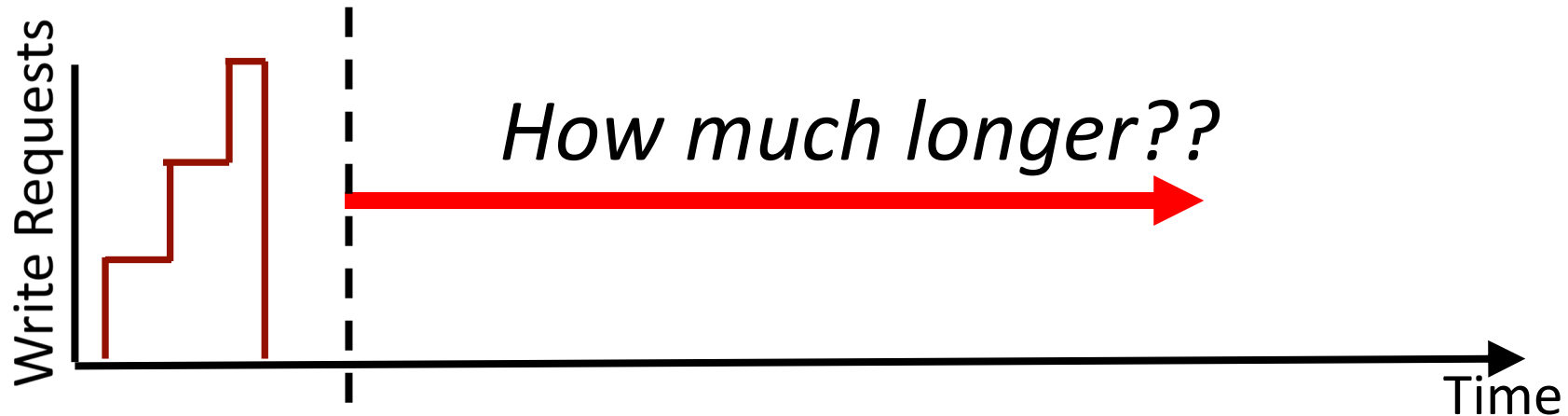
Does not test at every write



MEMCON *selectively* initiates testing when the write interval is *long enough* to *amortize* the cost of testing

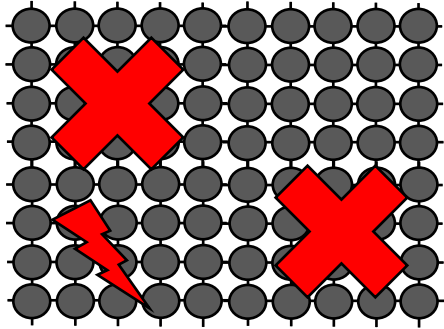
MEMCON: MECHANISM

MinWriteInterval is quite long



MEMCON *selectively* initiates testing
when the write interval is *long enough*
to amortize the cost of testing

How do we predict the interval on a write access?



DRAM

**MAKE DRAM
SCALABLE**

**System-Level
Detection and
Mitigation of
Failures**

**PROBLEM:
SCRAMBLED ADDRESS MAPPING**

**MEMCON: DRAM-Internal
Independent Detection**

CAL'16, MICRO'17

GOAL

KEY IDEA

CHALLENGE

MECHANISM

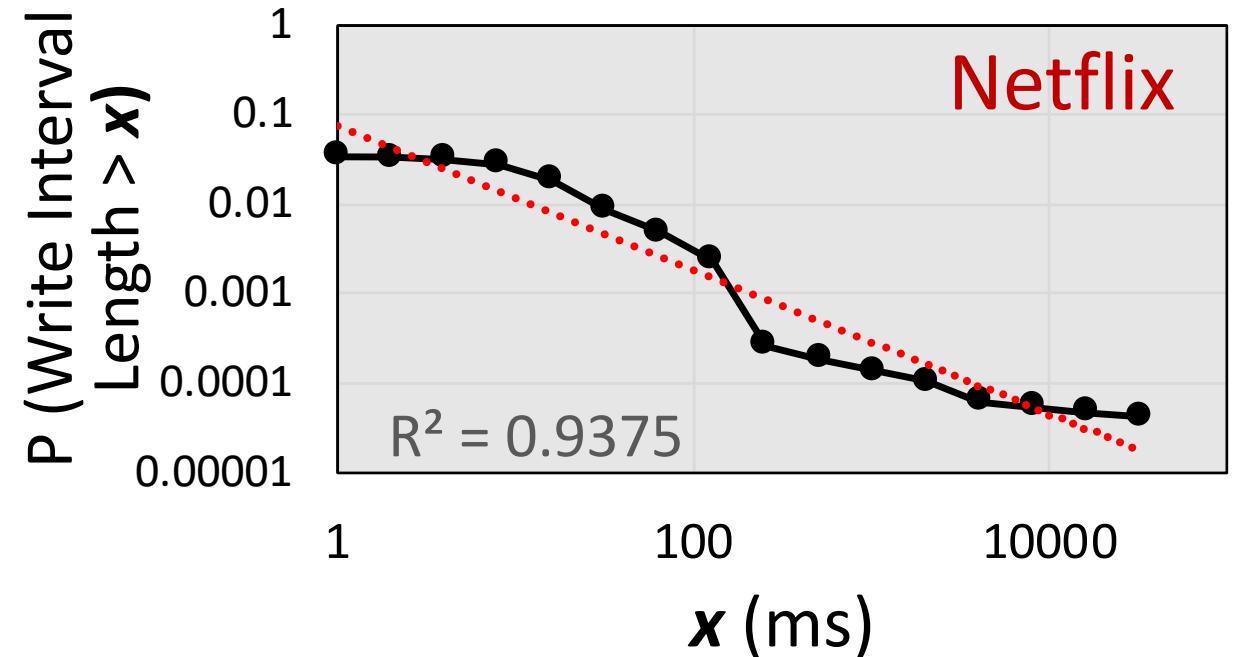
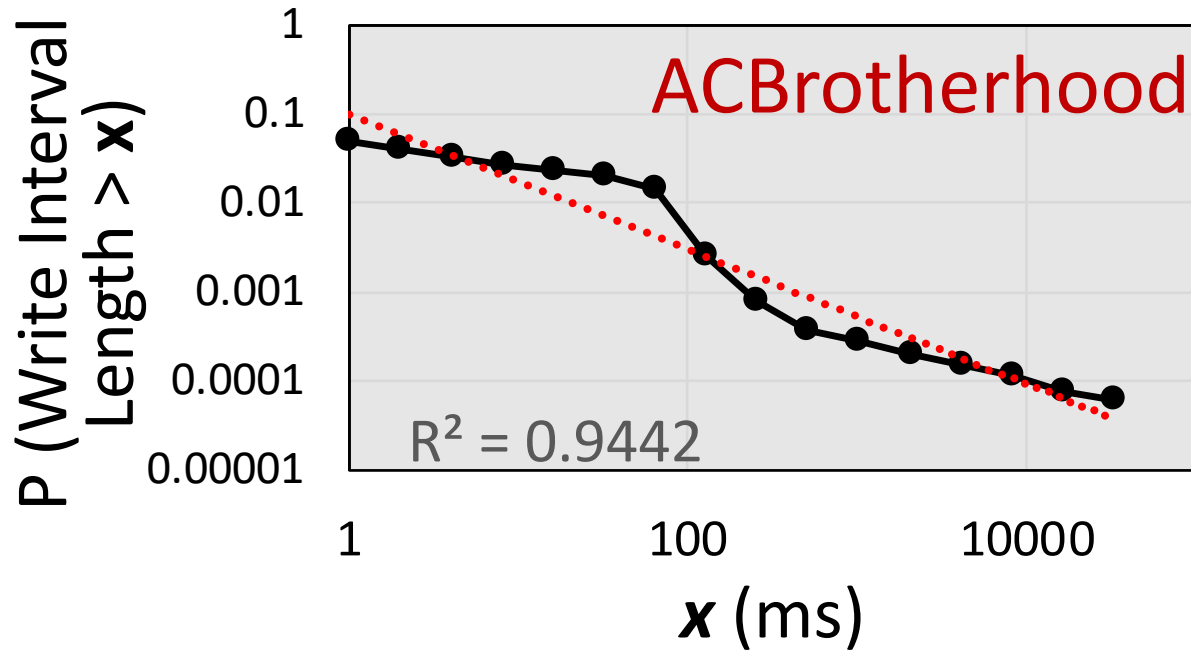
RESULTS



SYSMARK 2014

32 seconds of execution on a real machine
Profiled with a custom FPGA-based infrastructure

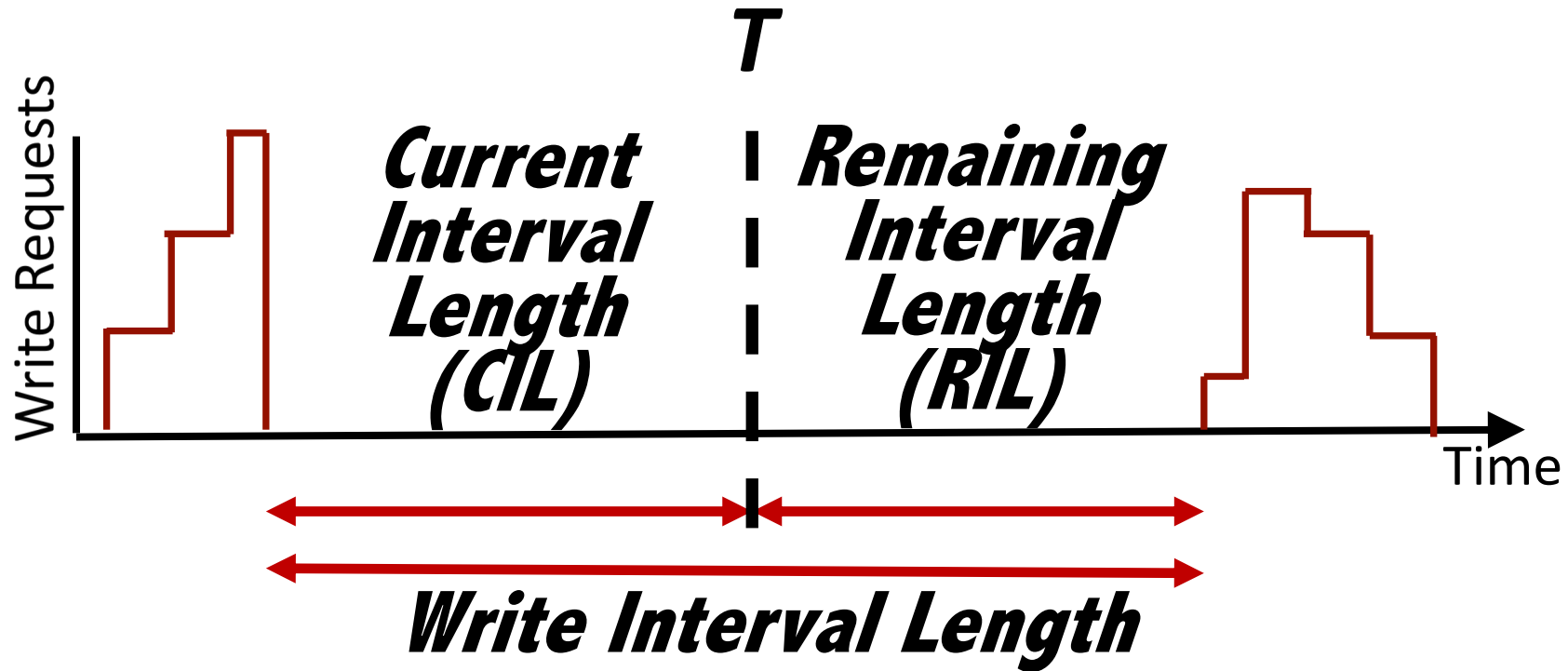
WRITE INTERVAL CHARACTERISTICS



Write intervals follow a Pareto distribution

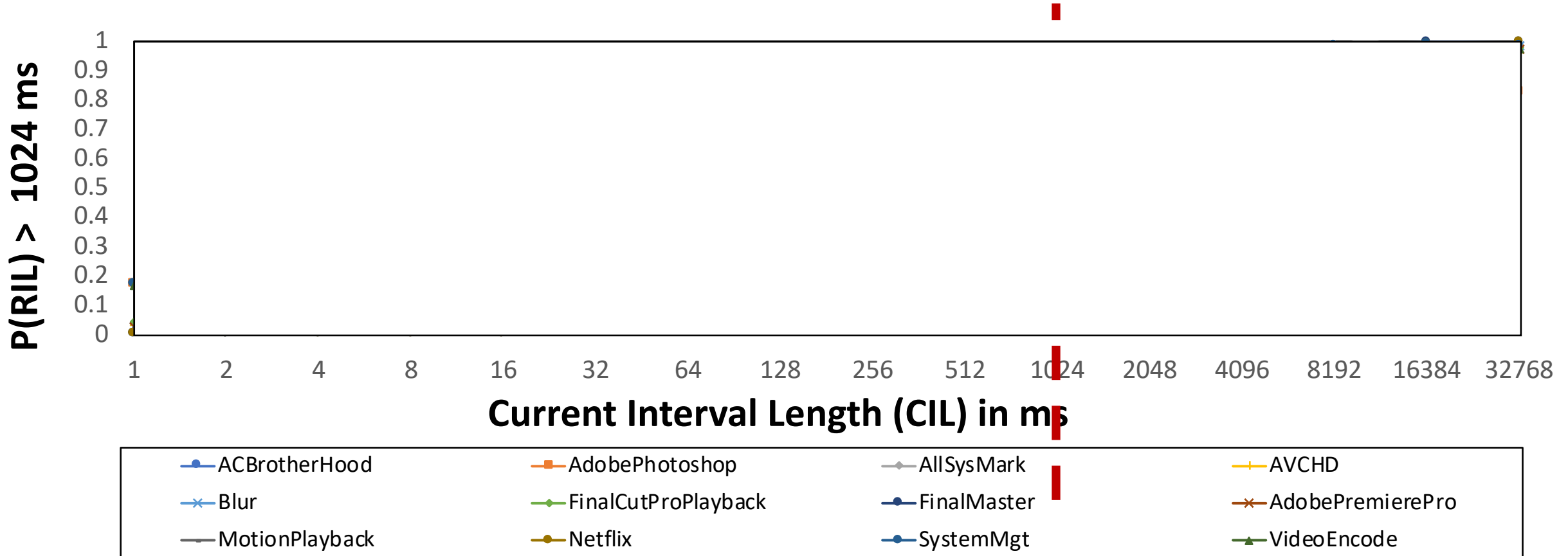
The longer the elapsed time after a write
→ The longer the write interval

WRITE INTERVAL CHARACTERISTICS



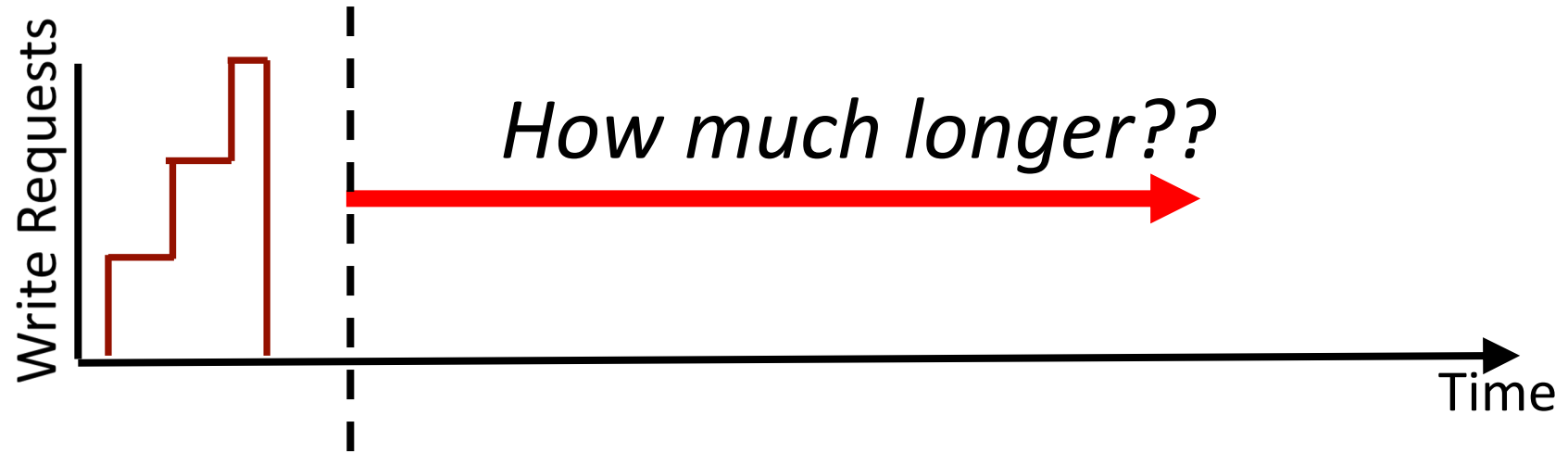
The longer the **CIL**
→ It is expected that the longer the **RIL**

WRITE INTERVAL CHARACTERISTICS

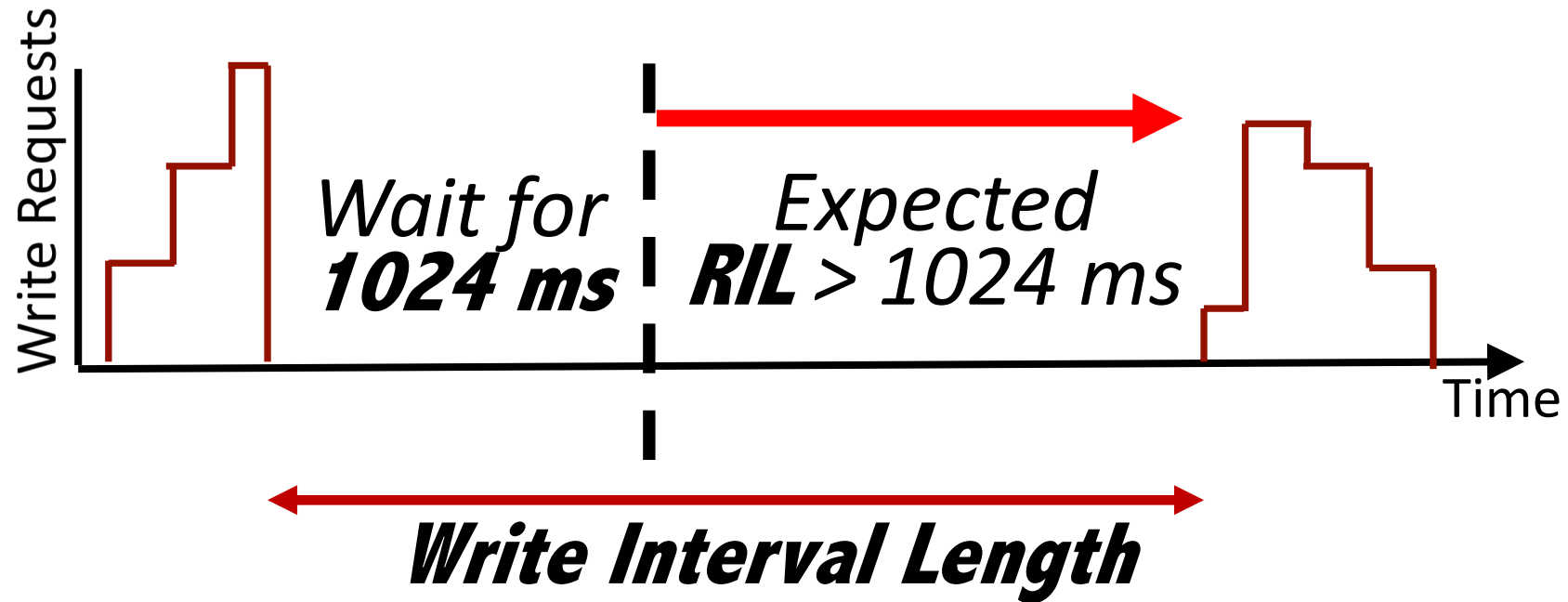


If the interval is already 1024 ms long, the probability that the remaining interval is greater than 1024 ms is on average 76%

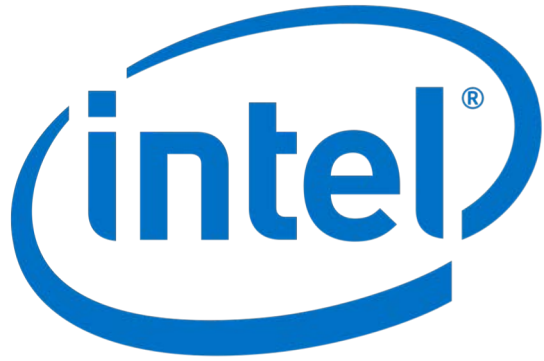
How do we predict the interval on a write access?



WRITE INTERVAL PREDICTION



After a write, wait for a CIL, where $P(RIL) > 1024$ is high
If idle, predict the interval will last more than 1024 ms



Microsoft[®]



**Stony Brook
University**

ETH zürich



PennState